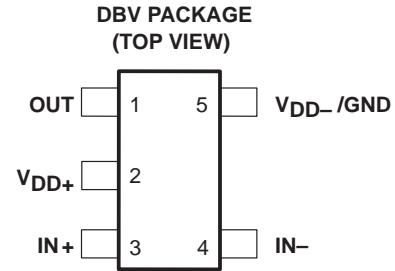


- Output Swing Includes Both Supply Rails
- Low Noise . . . 19 nV/√Hz Typ at f = 1 kHz
- Low Input Bias Current . . . 1 pA Typ
- Fully Specified for Single-Supply 3-V and 5-V Operation
- Very Low Power . . . 110 μA Typ
- Common-Mode Input Voltage Range Includes Negative Rail
- Wide Supply Voltage Range 2.7 V to 10 V
- Macromodel Included



### description

The TLV2721 is a single low-voltage operational amplifier available in the SOT-23 package. It offers a compromise between the ac performance and output drive of the TLV2731 and the micropower TLV2711.

It consumes only 150 μA (max) of supply current and is ideal for battery-powered applications. The device exhibits rail-to-rail output performance for increased dynamic range in single- or split-supply applications. The TLV2721 is fully characterized at 3 V and 5 V and is optimized for low-voltage applications.

The TLV2721, exhibiting high input impedance and low noise, is excellent for small-signal conditioning for high-impedance sources, such as piezoelectric transducers. Because of the micropower dissipation levels combined with 3-V operation, these devices work well in hand-held monitoring and remote-sensing applications. In addition, the rail-to-rail output feature with single or split supplies makes this family a great choice when interfacing with analog-to-digital converters (ADCs).

With a total area of 5.6mm<sup>2</sup>, the SOT-23 package only requires one third the board space of the standard 8-pin SOIC package. This ultra-small package allows designers to place single amplifiers very close to the signal source, minimizing noise pick-up from long PCB traces.

#### AVAILABLE OPTIONS

T <sub>A</sub>	V <sub>IO</sub> max AT 25°C	PACKAGED DEVICES	SYMBOL	CHIP FORM‡ (Y)
		SOT-23 (DBV)†		
0°C to 70°C	3 mV	TLV2721CDBV	VAKC	TLV2721Y
-40°C to 85°C	3 mV	TLV2721IDBV	VAKI	

† The DBV package available in tape and reel only.

‡ Chip forms are tested at T<sub>A</sub> = 25°C only.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

Advanced LinCMOS is a trademark of Texas Instruments Incorporated.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



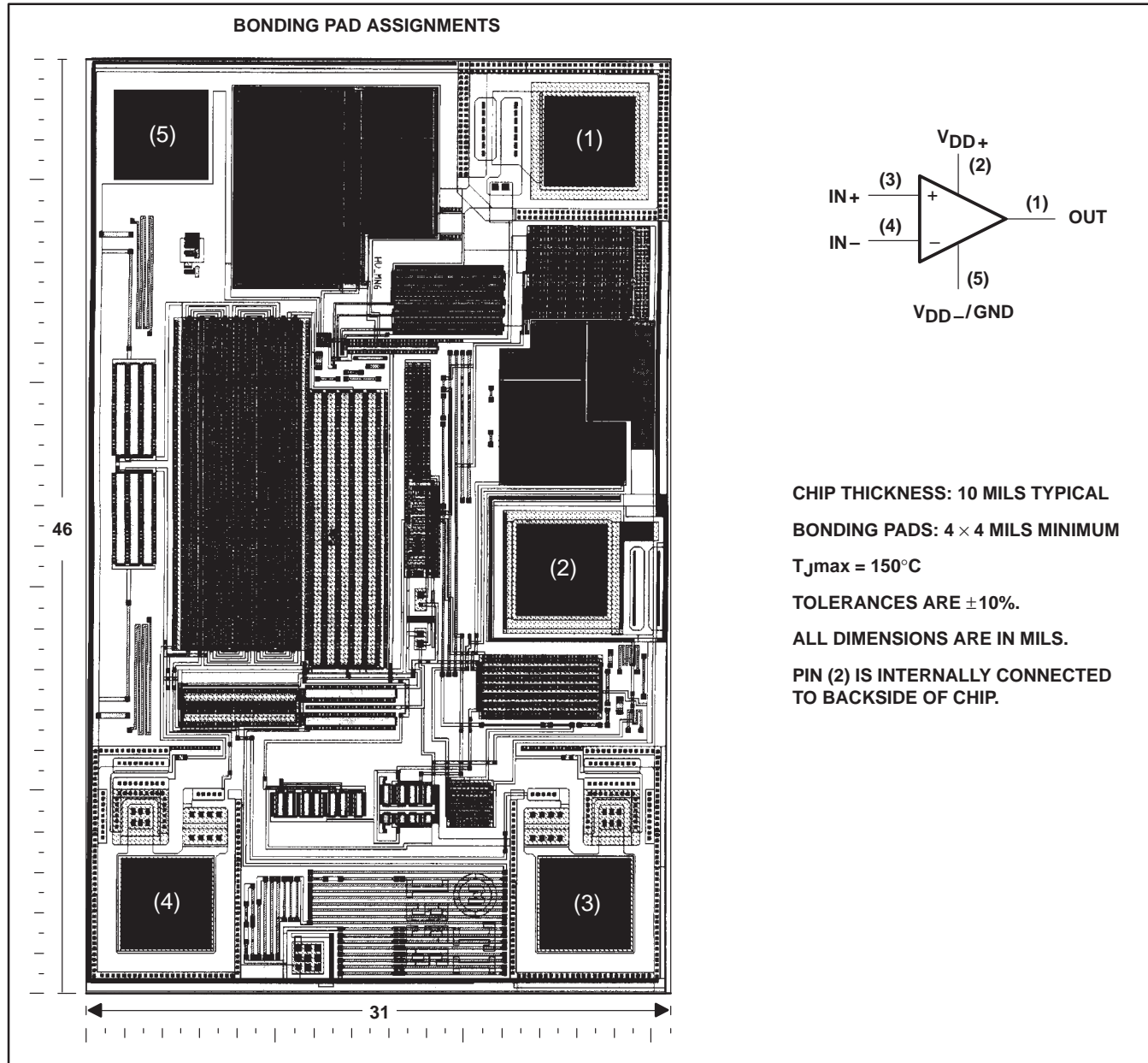
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Copyright © 1997, Texas Instruments Incorporated

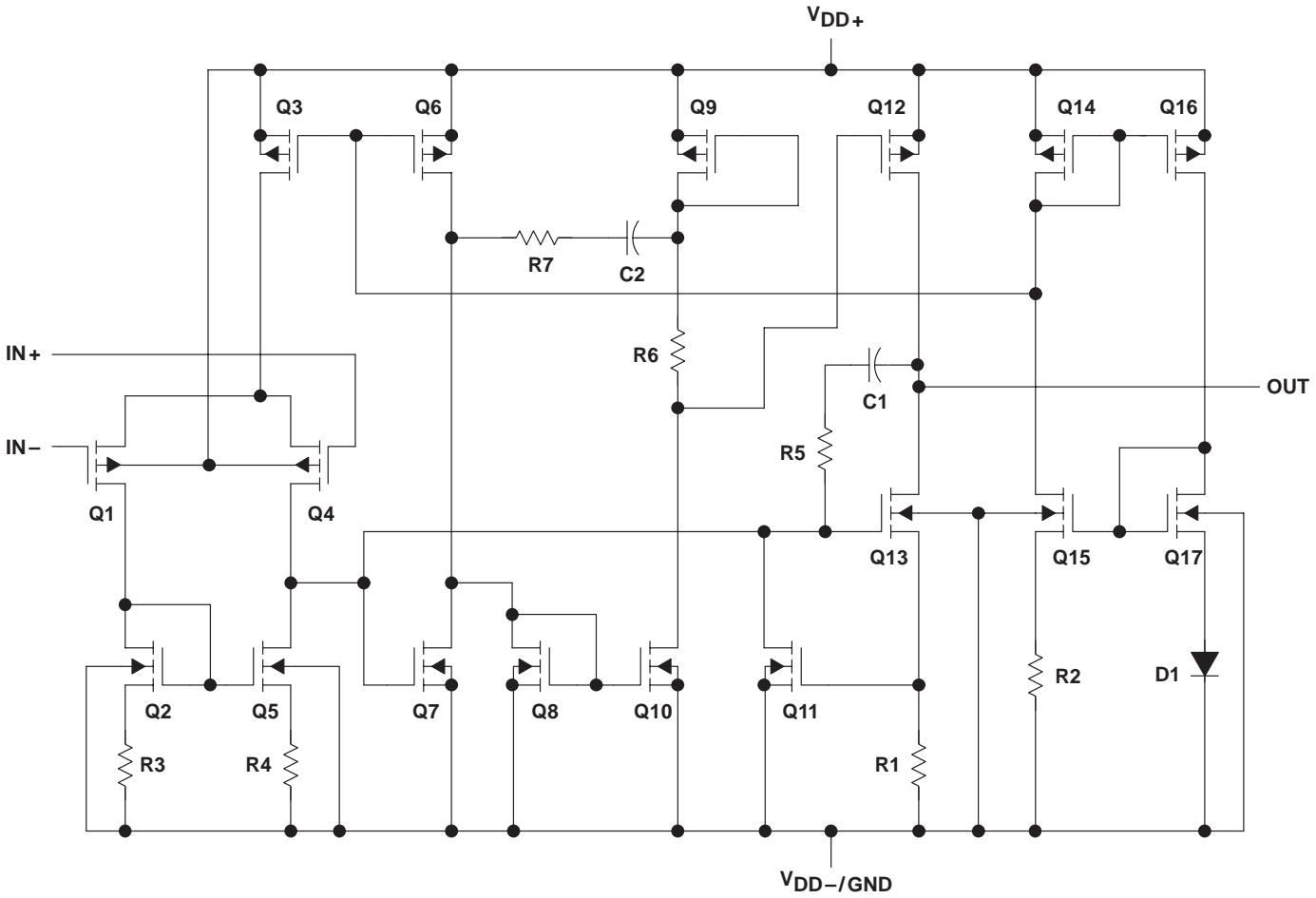
**TLV2721, TLV2721Y**  
**Advanced LinCMOS™ RAIL-TO-RAIL**  
**VERY LOW-POWER SINGLE OPERATIONAL AMPLIFIERS**  
 SLOS197 – AUGUST1997

**TLV2721Y chip information**

This chip, when properly assembled, displays characteristics similar to the TLV2721C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. This chip may be mounted with conductive epoxy or a gold-silicon preform.



equivalent schematic



COMPONENT COUNT†	
Transistors	23
Diodes	5
Resistors	11
Capacitors	2

† Includes both amplifiers and all ESD, bias, and trim circuitry

**TLV2721, TLV2721Y**  
**Advanced LinCMOS™ RAIL-TO-RAIL**  
**VERY LOW-POWER SINGLE OPERATIONAL AMPLIFIERS**  
 SLOS197 – AUGUST 1997

**absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†**

Supply voltage, $V_{DD}$ (see Note 1)	12 V
Differential input voltage, $V_{ID}$ (see Note 2)	$\pm V_{DD}$
Input voltage range, $V_I$ (any input, see Note 1)	-0.3 V to $V_{DD}$
Input current, $I_I$ (each input)	$\pm 5$ mA
Output current, $I_O$	$\pm 50$ mA
Total current into $V_{DD+}$	$\pm 50$ mA
Total current out of $V_{DD-}$	$\pm 50$ mA
Duration of short-circuit current (at or below) 25°C (see Note 3)	unlimited
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, $T_A$ : TLV2721C	0°C to 70°C
TLV2721I	-40°C to 85°C
Storage temperature range, $T_{stg}$	-65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: DBV package	260°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to  $V_{DD-}$ .  
 2. Differential voltages are at the noninverting input with respect to the inverting input. Excessive current flows when input is brought below  $V_{DD-} - 0.3$  V.  
 3. The output can be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

**DISSIPATION RATING TABLE**

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$ POWER RATING	$T_A = 85^\circ\text{C}$ POWER RATING
DBV	150 mW	1.2 mW/°C	96 mW	78 mW

**recommended operating conditions**

	TLV2721C		TLV2721I		UNIT
	MIN	MAX	MIN	MAX	
Supply voltage, $V_{DD}$ (see Note 1)	2.7	10	2.7	10	V
Input voltage range, $V_I$	$V_{DD-}$	$V_{DD+} - 1.3$	$V_{DD-}$	$V_{DD+} - 1.3$	V
Common-mode input voltage, $V_{IC}$	$V_{DD-}$	$V_{DD+} - 1.3$	$V_{DD-}$	$V_{DD+} - 1.3$	V
Operating free-air temperature, $T_A$	0	70	-40	85	°C

NOTE 1: All voltage values, except differential voltages, are with respect to  $V_{DD-}$ .



TLV2721, TLV2721Y  
Advanced LinCMOS™ RAIL-TO-RAIL  
VERY LOW-POWER SINGLE OPERATIONAL AMPLIFIERS  
SLOS197 – AUGUST 1997

electrical characteristics at specified free-air temperature,  $V_{DD} = 3\text{ V}$  (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A$ †	TLV2721C			TLV2721I			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
$V_{IO}$ Input offset voltage	$V_{DD\pm} = \pm 1.5\text{ V}$ , $V_O = 0$ , $V_{IC} = 0$ , $R_S = 50\ \Omega$	Full range	0.5		3	0.5		3	mV
$\alpha_{V_{IO}}$ Temperature coefficient of input offset voltage			1		1		$\mu\text{V}/^\circ\text{C}$		
Input offset voltage long-term drift (see Note 4)		25°C	0.003		0.003		$\mu\text{V}/\text{mo}$		
$I_{IO}$ Input offset current		25°C	0.5		0.5		pA		
		Full range	150		150				
$I_{IB}$ Input bias current		25°C	1		1		pA		
	Full range	150		150					
$V_{ICR}$ Common-mode input voltage range	$R_S = 50\ \Omega$ , $ V_{IO}  \leq 5\text{ mV}$	25°C	0 to 2	-0.3 to 2.2	0 to 2	-0.3 to 2.2	V		
		Full range	0 to 1.7	0 to 1.7	0 to 1.7	0 to 1.7			
$V_{OH}$ High-level output voltage	$I_{OH} = -100\ \mu\text{A}$ $I_{OH} = -400\ \mu\text{A}$	25°C	2.97		2.97		V		
		25°C	2.88		2.88				
		Full range	2.6		2.6				
$V_{OL}$ Low-level output voltage	$V_{IC} = 1.5\text{ V}$ , $I_{OL} = 50\ \mu\text{A}$ $V_{IC} = 1.5\text{ V}$ , $I_{OL} = 500\ \mu\text{A}$	25°C	15		15		mV		
		25°C	150		150				
		Full range	500		500				
$A_{VD}$ Large-signal differential voltage amplification	$V_{IC} = 1.5\text{ V}$ , $V_O = 1\text{ V to } 2\text{ V}$	25°C	$R_L = 2\text{ k}\Omega$ ‡		2 3		V/mV		
			Full range		1				
		25°C	$R_L = 1\text{ M}\Omega$ ‡		250				
$r_{id}$ Differential input resistance		25°C	$10^{12}$		$10^{12}$		$\Omega$		
$r_{ic}$ Common-mode input resistance		25°C	$10^{12}$		$10^{12}$		$\Omega$		
$c_{ic}$ Common-mode input capacitance	$f = 10\text{ kHz}$	25°C	6		6		pF		
$z_o$ Closed-loop output impedance	$f = 10\text{ kHz}$ , $A_V = 10$	25°C	90		90		$\Omega$		
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to } 1.7\text{ V}$ , $V_O = 1.5\text{ V}$ , $R_S = 50\ \Omega$	25°C	70	82	70	82	dB		
		Full range	65		65				
$k_{SVR}$ Supply voltage rejection ratio ( $\Delta V_{DD} / \Delta V_{IO}$ )	$V_{DD} = 2.7\text{ V to } 8\text{ V}$ , $V_{IC} = V_{DD}/2$ , No load	25°C	80	95	80	95	dB		
		Full range	80		80				
$I_{DD}$ Supply current	$V_O = 1.5\text{ V}$ , No load	25°C	100	150	100	150	$\mu\text{A}$		
		Full range	200		200				

† Full range for the TLV2721C is 0°C to 70°C. Full range for the TLV2721I is -40°C to 85°C.

‡ Referenced to 1.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at  $T_A = 150^\circ\text{C}$  extrapolated to  $T_A = 25^\circ\text{C}$  using the Arrhenius equation and assuming an activation energy of 0.96 eV.

**TLV2721, TLV2721Y**  
**Advanced LinCMOS™ RAIL-TO-RAIL**  
**VERY LOW-POWER SINGLE OPERATIONAL AMPLIFIERS**  
 SLOS197 – AUGUST 1997

operating characteristics at specified free-air temperature,  $V_{DD} = 3\text{ V}$

PARAMETER	TEST CONDITIONS	$T_A$ †	TLV2721C			TLV2721I			UNIT	
			MIN	TYP	MAX	MIN	TYP	MAX		
SR	Slew rate at unity gain $V_O = 1.1\text{ V to }1.9\text{ V}, R_L = 2\text{ k}\Omega^\ddagger, C_L = 100\text{ pF}^\ddagger$	25°C	0.1	0.25		0.1	0.25		V/ $\mu\text{s}$	
		Full range	0.05			0.05				
$V_n$	Equivalent input noise voltage $f = 10\text{ Hz}$ $f = 1\text{ kHz}$	25°C	120			120			nV/ $\sqrt{\text{Hz}}$	
		25°C	20			20				
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage $f = 0.1\text{ Hz to }1\text{ Hz}$ $f = 0.1\text{ Hz to }10\text{ Hz}$	25°C	680			680			mV	
		25°C	860			860				
$I_n$	Equivalent input noise current	25°C	0.6			0.6			fA/ $\sqrt{\text{Hz}}$	
THD+N	Total harmonic distortion plus noise $V_O = 1\text{ V to }2\text{ V}, f = 20\text{ kHz}, R_L = 2\text{ k}\Omega^\ddagger$ $V_O = 1\text{ V to }2\text{ V}, f = 20\text{ kHz}, R_L = 2\text{ k}\Omega^\S$	25°C	$A_V = 1$	2.52%			2.52%			
			$A_V = 10$	7.01%			7.01%			
		25°C	$A_V = 1$	0.076%			0.076%			
			$A_V = 10$	0.147%			0.147%			
Gain-bandwidth product	$f = 1\text{ kHz}, C_L = 100\text{ pF}^\ddagger, R_L = 2\text{ k}\Omega^\ddagger$	25°C	480			480			kHz	
BOM	Maximum output-swing bandwidth $V_{O(PP)} = 1\text{ V}, R_L = 2\text{ k}\Omega^\ddagger, A_V = 1, C_L = 100\text{ pF}^\ddagger$	25°C	30			30			kHz	
$t_s$	Settling time $A_V = -1, \text{ Step} = 1\text{ V to }2\text{ V}, R_L = 2\text{ k}\Omega^\ddagger, C_L = 100\text{ pF}^\ddagger$	25°C	To 0.1%	4.5			4.5			$\mu\text{s}$
		25°C	To 0.01%	6.8			6.8			$\mu\text{s}$
$\phi_m$	Phase margin at unity gain $R_L = 2\text{ k}\Omega^\ddagger, C_L = 100\text{ pF}^\ddagger$	25°C	53°			53°				
	Gain margin	25°C	12			12			dB	

† Full range is  $-40^\circ\text{C}$  to  $85^\circ\text{C}$ .

‡ Referenced to 1.5 V

§ Referenced to 0 V



TLV2721, TLV2721Y  
Advanced LinCMOS™ RAIL-TO-RAIL  
VERY LOW-POWER SINGLE OPERATIONAL AMPLIFIERS  
SLOS197 – AUGUST 1997

electrical characteristics at specified free-air temperature,  $V_{DD} = 5\text{ V}$  (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A$ †	TLV2721C			TLV2721I			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
$V_{IO}$ Input offset voltage	$V_{DD\pm} = \pm 2.5\text{ V}$ , $V_O = 0$ , $V_{IC} = 0$ , $R_S = 50\ \Omega$	Full range	0.5		3	0.5		3	mV
$\alpha_{V_{IO}}$ Temperature coefficient of input offset voltage			1		1		$\mu\text{V}/^\circ\text{C}$		
Input offset voltage long-term drift (see Note 4)		25°C	0.003		0.003		$\mu\text{V}/\text{mo}$		
$I_{IO}$ Input offset current		25°C	0.5		0.5		pA		
		Full range	150		150				
$I_{IB}$ Input bias current		25°C	1		1		pA		
	Full range	150		150					
$V_{ICR}$ Common-mode input voltage range	$R_S = 50\ \Omega$ , $ V_{IO}  \leq 5\text{ mV}$	25°C	0 to 4	-0.3 to 4.2	0 to 4	-0.3 to 4.2	V		
		Full range	0 to 3.5	0 to 3.5	0 to 3.5	0 to 3.5			
$V_{OH}$ High-level output voltage	$I_{OH} = -500\ \mu\text{A}$	25°C	4.75	4.88	4.75	4.88	V		
	$I_{OH} = -1\text{ mA}$		4.6	4.76	4.6	4.76			
$V_{OL}$ Low-level output voltage	$V_{IC} = 2.5\text{ V}$ , $I_{OL} = 50\ \mu\text{A}$	25°C	12		12		mV		
	$V_{IC} = 2.5\text{ V}$ , $I_{OL} = 500\ \mu\text{A}$	25°C	120		120				
	Full range	500		500					
$A_{VD}$ Large-signal differential voltage amplification	$V_{IC} = 2.5\text{ V}$ , $V_O = 1\text{ V to } 4\text{ V}$	25°C	$R_L = 2\text{ k}\Omega$ ‡		3 5		V/mV		
			Full range	1		1			
		25°C	$R_L = 1\text{ M}\Omega$ ‡		800			800	
$r_{id}$ Differential input resistance		25°C	$10^{12}$		$10^{12}$		$\Omega$		
$r_{ic}$ Common-mode input resistance		25°C	$10^{12}$		$10^{12}$		$\Omega$		
$C_{ic}$ Common-mode input capacitance	$f = 10\text{ kHz}$	25°C	6		6		pF		
$Z_o$ Closed-loop output impedance	$f = 10\text{ kHz}$ , $A_V = 10$	25°C	70		70		$\Omega$		
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to } 2.7\text{ V}$ , $V_O = 1.5\text{ V}$ , $R_S = 50\ \Omega$	25°C	70	85	70	85	dB		
		Full range	65		65				
$k_{SVR}$ Supply voltage rejection ratio ( $\Delta V_{DD} / \Delta V_{IO}$ )	$V_{DD} = 4.4\text{ V to } 8\text{ V}$ , $V_{IC} = V_{DD}/2$ , No load	25°C	80	95	80	95	dB		
		Full range	80		80				
$I_{DD}$ Supply current	$V_O = 2.5\text{ V}$ , No load	25°C	110	150	110	150	$\mu\text{A}$		
		Full range	200		200				

† Full range for the TLV2721C is 0°C to 70°C. Full range for the TLV2721I is -40°C to 85°C.

‡ Referenced to 2.5 V

NOTE 5: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at  $T_A = 150^\circ\text{C}$  extrapolated to  $T_A = 25^\circ\text{C}$  using the Arrhenius equation and assuming an activation energy of 0.96 eV.

**TLV2721, TLV2721Y**  
**Advanced LinCMOS™ RAIL-TO-RAIL**  
**VERY LOW-POWER SINGLE OPERATIONAL AMPLIFIERS**  
 SLOS197 – AUGUST 1997

**operating characteristics at specified free-air temperature,  $V_{DD} = 5\text{ V}$**

PARAMETER	TEST CONDITIONS	$T_A$ †	TLV2721C			TLV2721I			UNIT	
			MIN	TYP	MAX	MIN	TYP	MAX		
SR	Slew rate at unity gain $V_O = 1.5\text{ V to }3.5\text{ V}, R_L = 2\text{ k}\Omega^\ddagger, C_L = 100\text{ pF}^\ddagger$	25°C	0.1	0.25		0.1	0.25		V/ $\mu$ s	
		Full range	0.05			0.05				
$V_n$	Equivalent input noise voltage $f = 10\text{ Hz}$ $f = 1\text{ kHz}$	25°C	90			90			nV/ $\sqrt{\text{Hz}}$	
		25°C	19			19				
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage $f = 0.1\text{ Hz to }1\text{ Hz}$ $f = 0.1\text{ Hz to }10\text{ Hz}$	25°C	800			800			mV	
		25°C	960			960				
$I_n$	Equivalent input noise current	25°C	0.6			0.6			fA/ $\sqrt{\text{Hz}}$	
THD+N	$V_O = 1.5\text{ V to }3.5\text{ V}, f = 20\text{ kHz}, R_L = 2\text{ k}\Omega^\ddagger$	25°C	$A_V = 1$	2.45%			2.45%			
			$A_V = 10$	5.54%			5.54%			
	25°C	$V_O = 1.5\text{ V to }3.5\text{ V}, f = 20\text{ kHz}, R_L = 2\text{ k}\Omega^\S$	$A_V = 1$	0.142%			0.142%			
			$A_V = 10$	0.257%			0.257%			
Gain-bandwidth product	$f = 1\text{ kHz}, C_L = 100\text{ pF}^\ddagger, R_L = 2\text{ k}\Omega^\ddagger$	25°C	510			510			kHz	
BOM	Maximum output-swing bandwidth $V_{O(PP)} = 1\text{ V}, R_L = 2\text{ k}\Omega^\ddagger, A_V = 1, C_L = 100\text{ pF}^\ddagger$	25°C	40			40			kHz	
$t_s$	Settling time $A_V = -1, \text{ Step} = 1.5\text{ V to }3.5\text{ V}, R_L = 2\text{ k}\Omega^\ddagger, C_L = 100\text{ pF}^\ddagger$	25°C	6.8			6.8			$\mu$ s	
		25°C	9.2			9.2				
$\phi_m$	Phase margin at unity gain $R_L = 2\text{ k}\Omega^\ddagger, C_L = 100\text{ pF}^\ddagger$	25°C	53°			53°				
		25°C	12			12				
	Gain margin	25°C	12			12			dB	

† Full range is  $-40^\circ\text{C to }85^\circ\text{C}$ .

‡ Referenced to 2.5 V

§ Referenced to 0 V





**electrical characteristics at  $V_{DD} = 3\text{ V}$ ,  $T_A = 25^\circ\text{C}$  (unless otherwise noted)**

PARAMETER	TEST CONDITIONS	TLV2721Y			UNIT
		MIN	TYP	MAX	
$V_{IO}$ Input offset voltage	$V_{DD} \pm = \pm 1.5\text{ V}$ , $R_S = 50\ \Omega$	$V_{IC} = 0$ , $V_O = 0$	620		$\mu\text{V}$
$I_{IO}$ Input offset current			0.5		$\text{pA}$
$I_{IB}$ Input bias current			1		$\text{pA}$
$V_{ICR}$ Common-mode input voltage range	$ V_{IO}  \leq 5\text{ mV}$ , $R_S = 50\ \Omega$		-0.3 to 2.2	$\text{V}$	
$V_{OH}$ High-level output voltage	$I_{OH} = -100\ \mu\text{A}$		2.97	$\text{V}$	
$V_{OL}$ Low-level output voltage	$V_{IC} = 1.5\text{ V}$ , $I_{OL} = 50\ \mu\text{A}$		15	$\text{mV}$	
	$V_{IC} = 1.5\text{ V}$ , $I_{OL} = 500\ \mu\text{A}$		150		
$A_{VD}$ Large-signal differential voltage amplification	$V_O = 1\text{ V to } 2\text{ V}$	$R_L = 2\text{ k}\Omega^\dagger$	3		$\text{V/mV}$
		$R_L = 1\text{ M}\Omega^\dagger$	250		
$r_{id}$ Differential input resistance			$10^{12}$	$\Omega$	
$r_{ic}$ Common-mode input resistance			$10^{12}$	$\Omega$	
$c_{ic}$ Common-mode input capacitance	$f = 10\text{ kHz}$		6	$\text{pF}$	
$z_o$ Closed-loop output impedance	$f = 10\text{ kHz}$ , $A_V = 10$		90	$\Omega$	
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to } 1.7\text{ V}$ , $V_O = 0$ , $R_S = 50\ \Omega$		82	$\text{dB}$	
$k_{SVR}$ Supply voltage rejection ratio ( $\Delta V_{DD}/\Delta V_{IO}$ )	$V_{DD} = 2.7\text{ V to } 8\text{ V}$ , $V_{IC} = 0$ , No load		95	$\text{dB}$	
$I_{DD}$ Supply current	$V_O = 0$ , No load		100	$\mu\text{A}$	

† Referenced to 1.5 V

**electrical characteristics at  $V_{DD} = 5\text{ V}$ ,  $T_A = 25^\circ\text{C}$  (unless otherwise noted)**

PARAMETER	TEST CONDITIONS	TLV2721Y			UNIT
		MIN	TYP	MAX	
$V_{IO}$ Input offset voltage	$V_{DD} \pm = \pm 1.5\text{ V}$ , $R_S = 50\ \Omega$	$V_{IC} = 0$ , $V_O = 0$	610		$\mu\text{V}$
$I_{IO}$ Input offset current			0.5		$\text{pA}$
$I_{IB}$ Input bias current			1		$\text{pA}$
$V_{ICR}$ Common-mode input voltage range	$ V_{IO}  \leq 5\text{ mV}$ , $R_S = 50\ \Omega$		-0.3 to 4.2	$\text{V}$	
$V_{OH}$ High-level output voltage	$I_{OH} = -500\ \mu\text{A}$		4.88	$\text{V}$	
$V_{OL}$ Low-level output voltage	$V_{IC} = 2.5\text{ V}$ , $I_{OL} = 50\ \mu\text{A}$		12	$\text{mV}$	
	$V_{IC} = 2.5\text{ V}$ , $I_{OL} = 500\ \mu\text{A}$		120		
$A_{VD}$ Large-signal differential voltage amplification	$V_O = 1\text{ V to } 4\text{ V}$	$R_L = 2\text{ k}\Omega^\dagger$	5		$\text{V/mV}$
		$R_L = 1\text{ M}\Omega^\dagger$	800		
$r_{id}$ Differential input resistance			$10^{12}$	$\Omega$	
$r_{ic}$ Common-mode input resistance			$10^{12}$	$\Omega$	
$c_{ic}$ Common-mode input capacitance	$f = 10\text{ kHz}$		6	$\text{pF}$	
$z_o$ Closed-loop output impedance	$f = 10\text{ kHz}$ , $A_V = 10$		70	$\Omega$	
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to } 1.7\text{ V}$ , $V_O = 0$ , $R_S = 50\ \Omega$		85	$\text{dB}$	
$k_{SVR}$ Supply voltage rejection ratio ( $\Delta V_{DD}/\Delta V_{IO}$ )	$V_{DD} = 2.7\text{ V to } 8\text{ V}$ , $V_{IC} = 0$ , No load		95	$\text{dB}$	
$I_{DD}$ Supply current	$V_O = 0$ , No load		110	$\mu\text{A}$	

† Referenced to 2.5 V

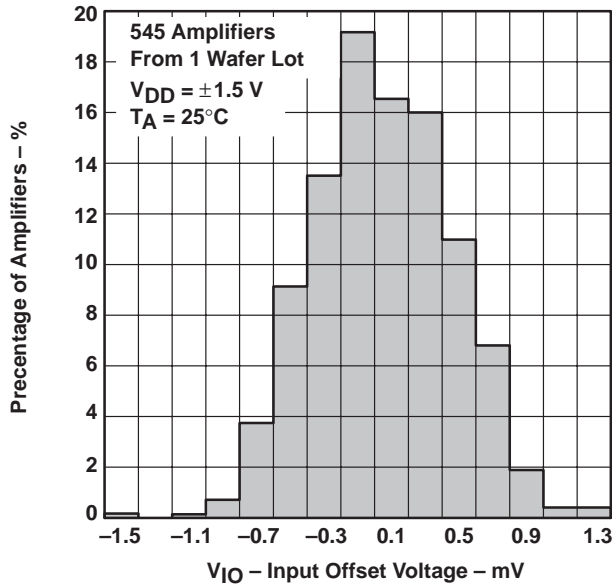
**TYPICAL CHARACTERISTICS**

**Table of Graphs**

		<b>FIGURE</b>	
$V_{IO}$	Input offset voltage	Distribution vs Common-mode input voltage	1, 2 3, 4
$\alpha V_{IO}$	Input offset voltage temperature coefficient	Distribution	5, 6
$I_{IB}/I_{IO}$	Input bias and input offset currents	vs Free-air temperature	7
$V_I$	Input voltage	vs Supply voltage vs Free-air temperature	8 9
$V_{OH}$	High-level output voltage	vs High-level output current	10, 13
$V_{OL}$	Low-level output voltage	vs Low-level output current	11, 12, 14
$V_{O(PP)}$	Maximum peak-to-peak output voltage	vs Frequency	15
$I_{OS}$	Short-circuit output current	vs Supply voltage vs Free-air temperature	16 17
$V_O$	Output voltage	vs Differential input voltage	18, 19
$A_{VD}$	Differential voltage amplification	vs Load resistance	20
$A_{VD}$	Large signal differential voltage amplification	vs Frequency vs Free-air temperature	21, 22 23, 24
$z_o$	Output impedance	vs Frequency	25, 26
CMRR	Common-mode rejection ratio	vs Frequency vs Free-air temperature	27 28
$k_{SVR}$	Supply-voltage rejection ratio	vs Frequency vs Free-air temperature	29, 30 31
$I_{DD}$	Supply current	vs Supply voltage	32
SR	Slew rate	vs Load capacitance vs Free-air temperature	33 34
$V_O$	Inverting large-signal pulse response	vs Time	35, 36
$V_O$	Voltage-follower large-signal pulse response	vs Time	37, 38
$V_O$	Inverting small-signal pulse response	vs Time	39, 40
$V_O$	Voltage-follower small-signal pulse response	vs Time	41, 42
$V_n$	Equivalent input noise voltage	vs Frequency	43, 44
	Input noise voltage (referred to input)	Over a 10-second period	45
THD + N	Total harmonic distortion plus noise	vs Frequency	46
	Gain-bandwidth product	vs Free-air temperature vs Supply voltage	47 48
$\phi_m$	Phase margin	vs Frequency vs Load capacitance	21, 22 51, 52
	Gain margin	vs Load capacitance	49, 50
$B_1$	Unity-gain bandwidth	vs Load capacitance	53, 54

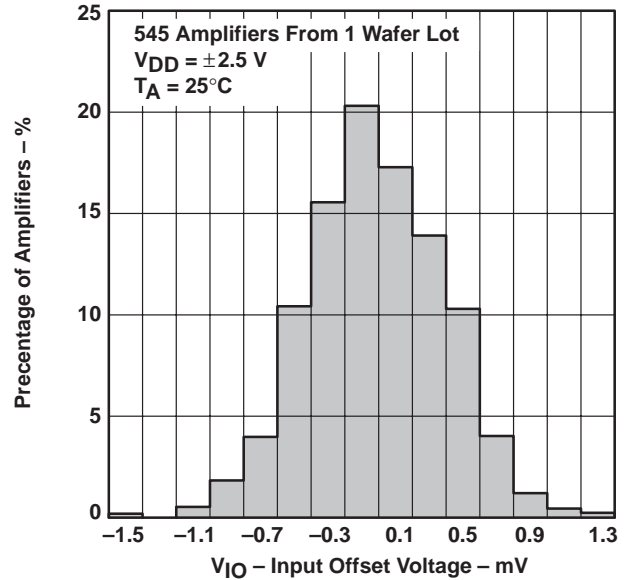
**TYPICAL CHARACTERISTICS**

**DISTRIBUTION OF TLV2721  
INPUT OFFSET VOLTAGE**



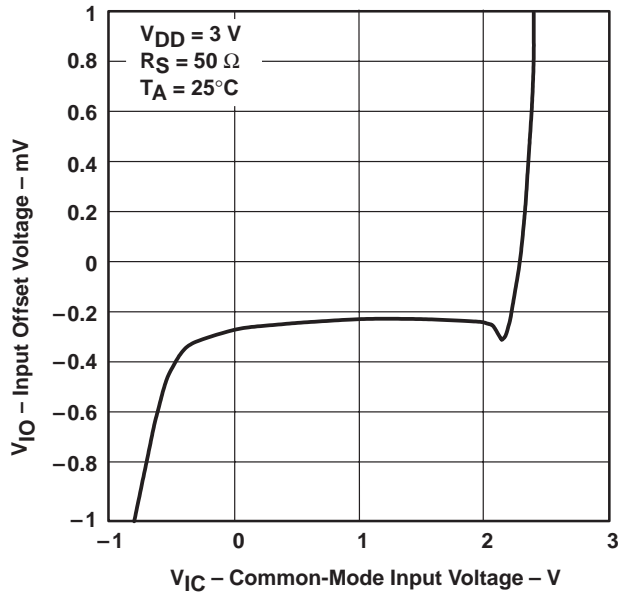
**Figure 1**

**DISTRIBUTION OF TLV2721  
INPUT OFFSET VOLTAGE**



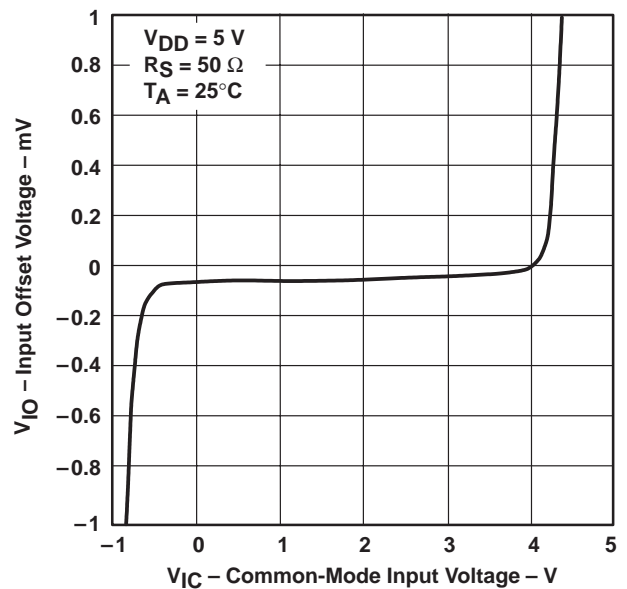
**Figure 2**

**INPUT OFFSET VOLTAGE†  
vs  
COMMON-MODE INPUT VOLTAGE**



**Figure 3**

**INPUT OFFSET VOLTAGE†  
vs  
COMMON-MODE INPUT VOLTAGE**



**Figure 4**

† For all curves where  $V_{DD} = 5\text{ V}$ , all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3\text{ V}$ , all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

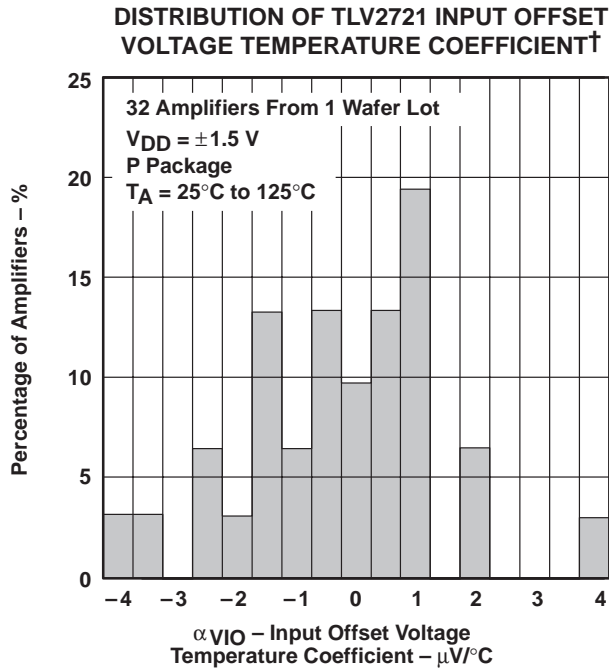


Figure 5

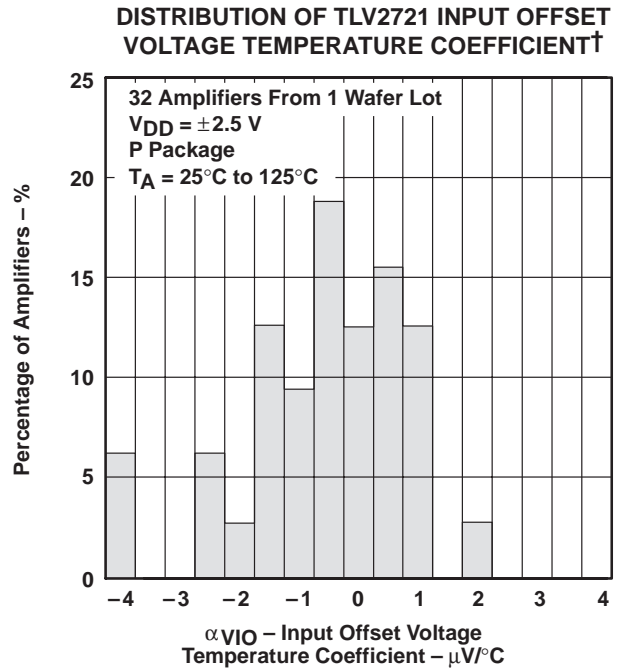


Figure 6

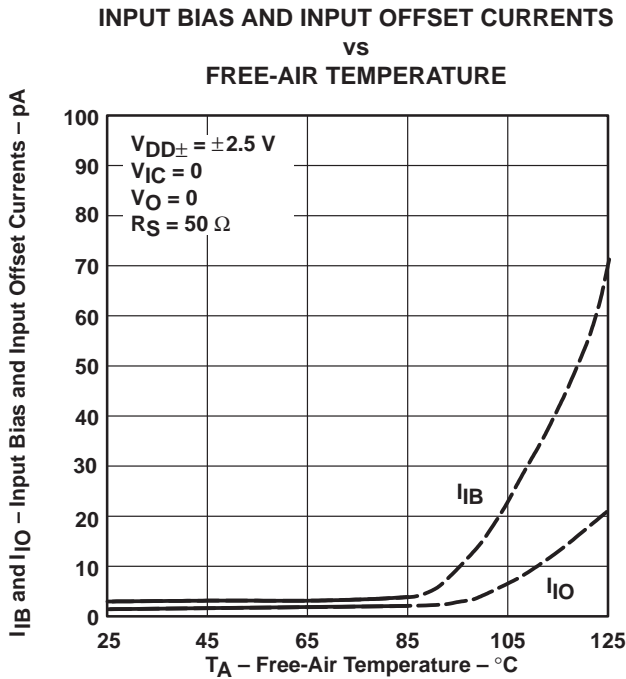


Figure 7

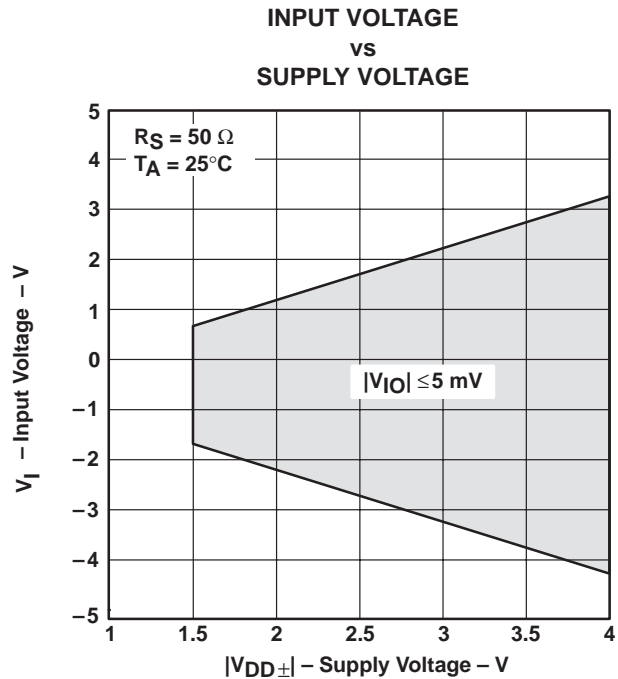
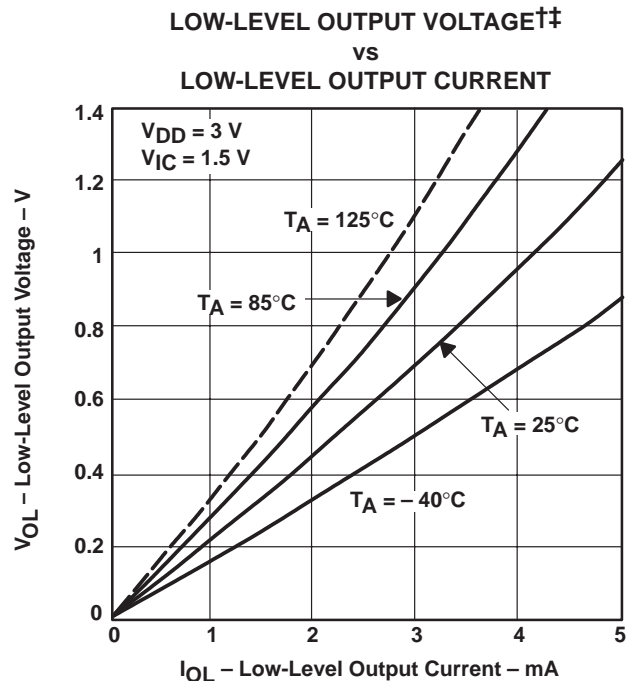
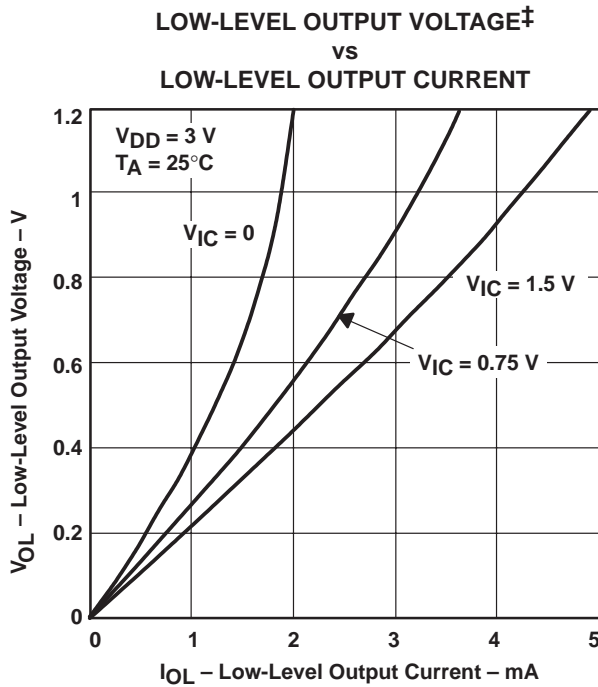
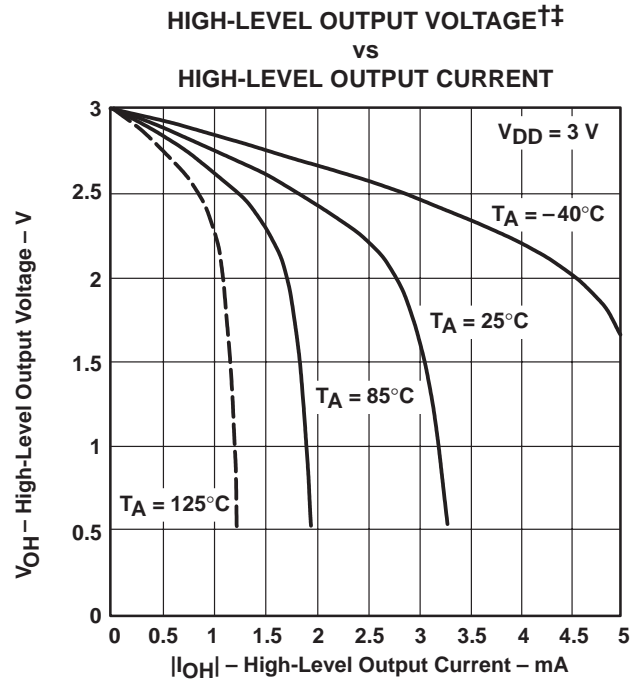
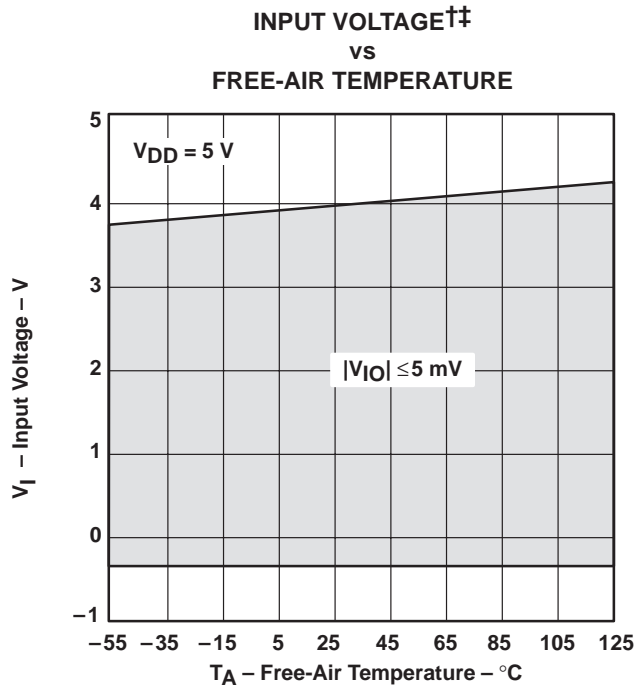


Figure 8

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS



† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.  
†† For all curves where  $V_{DD} = 5\text{ V}$ , all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3\text{ V}$ , all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

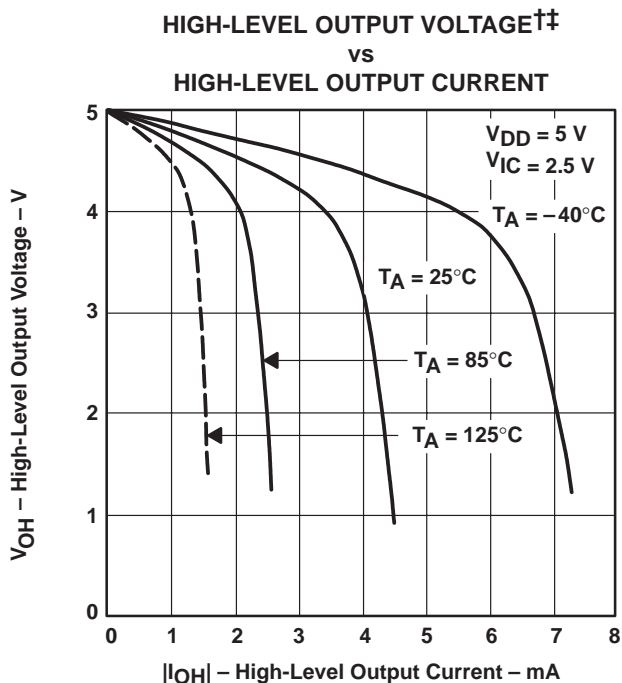


Figure 13

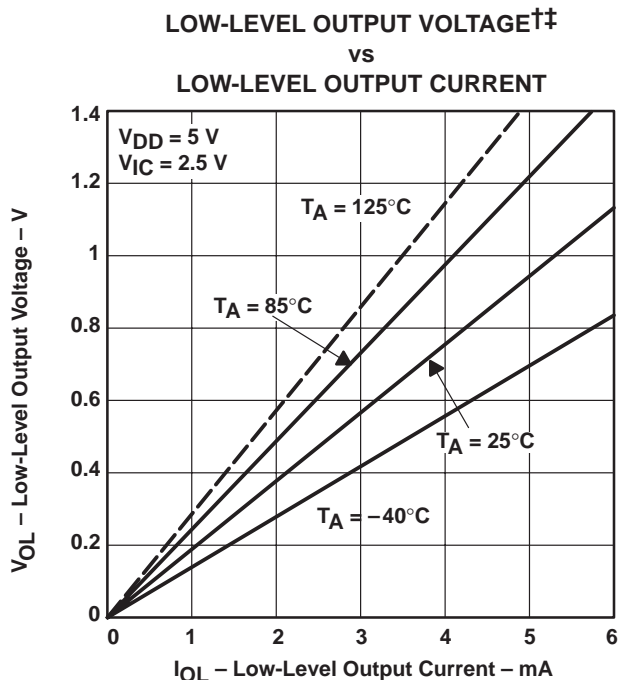


Figure 14

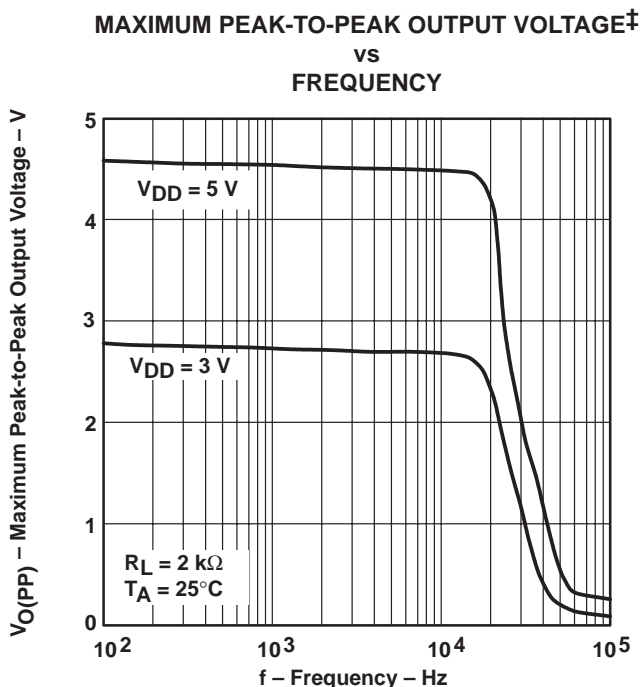


Figure 15

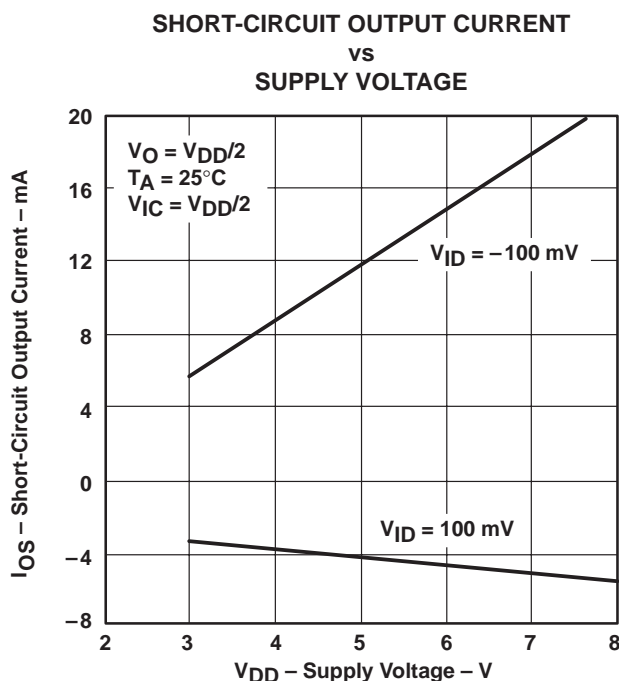
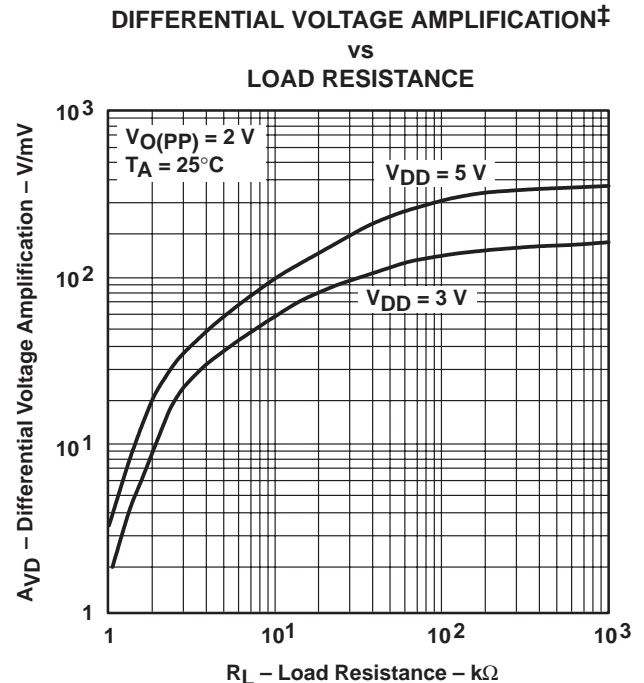
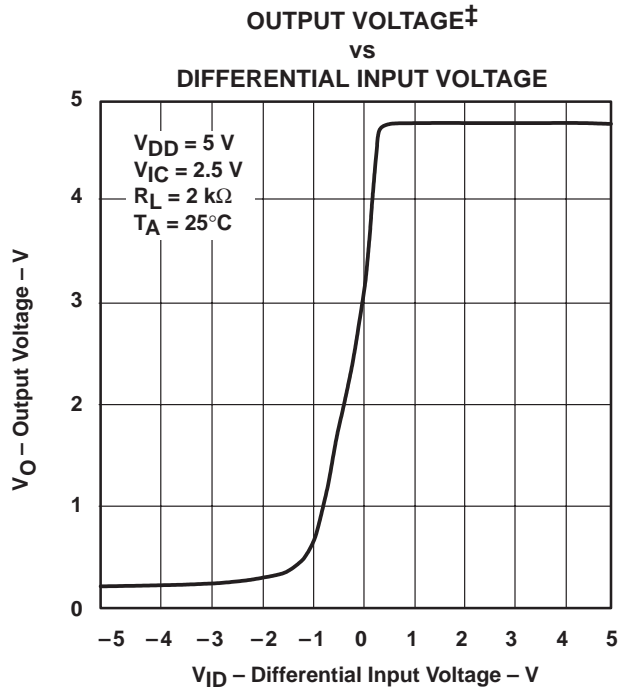
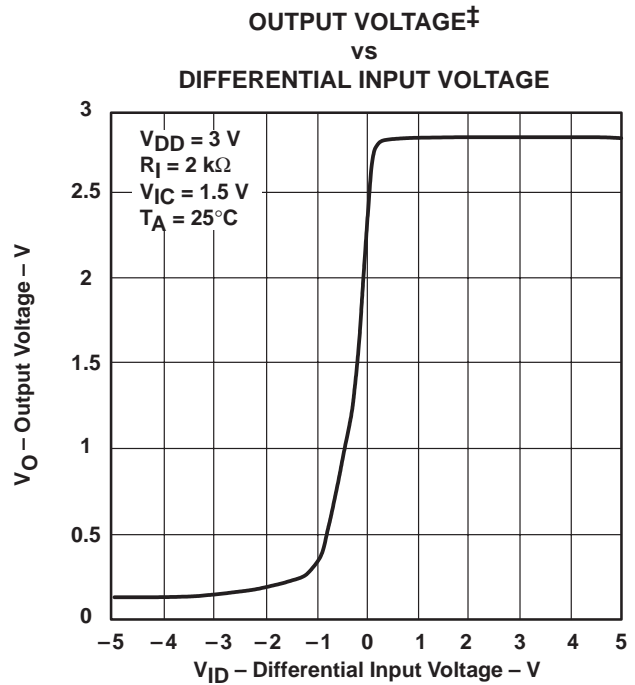
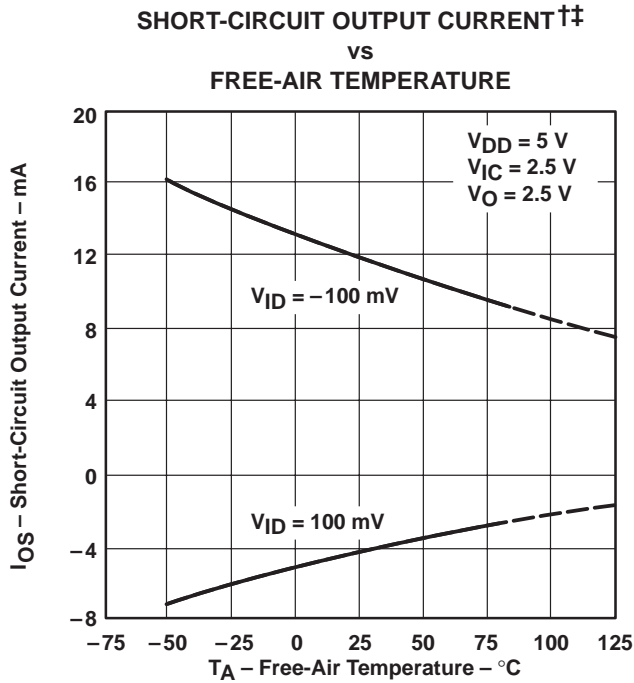


Figure 16

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.  
 ‡ For all curves where  $V_{DD} = 5\text{ V}$ , all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3\text{ V}$ , all loads are referenced to 1.5 V.

**TYPICAL CHARACTERISTICS**



† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

†† For all curves where  $V_{DD} = 5\text{ V}$ , all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3\text{ V}$ , all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

LARGE-SIGNAL DIFFERENTIAL VOLTAGE†  
 AMPLIFICATION AND PHASE MARGIN  
 VS  
 FREQUENCY

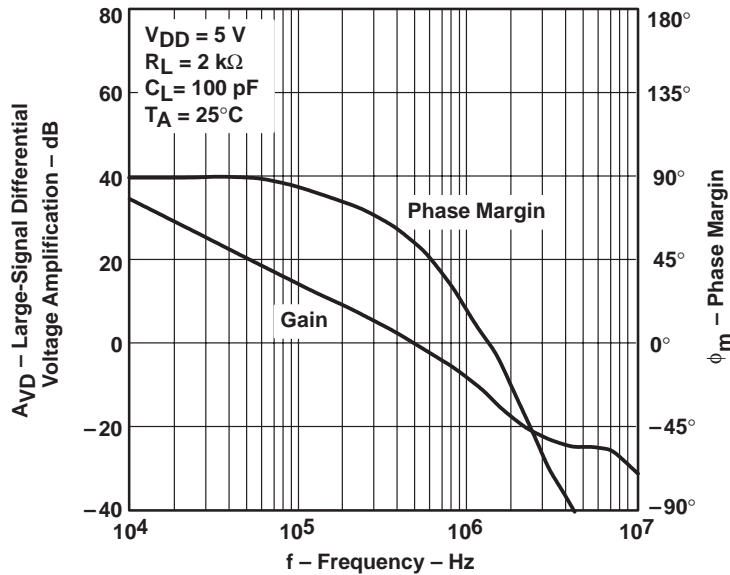


Figure 21

LARGE-SIGNAL DIFFERENTIAL VOLTAGE  
 AMPLIFICATION AND PHASE MARGIN†  
 VS  
 FREQUENCY

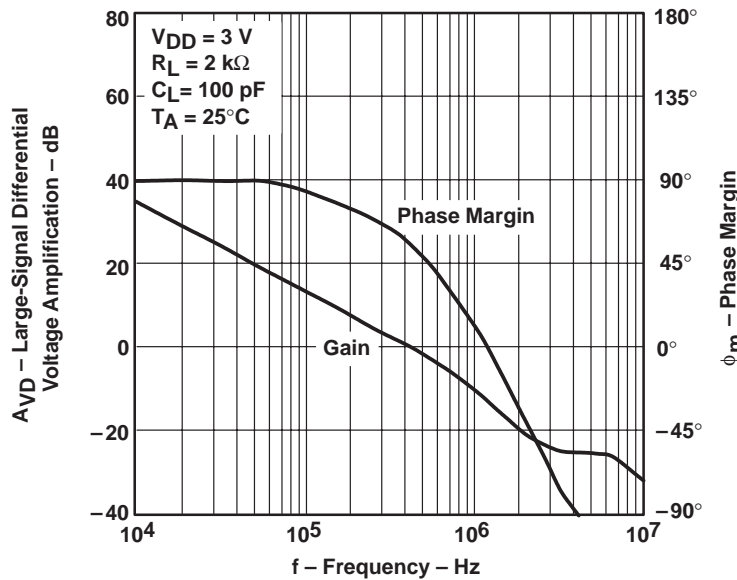
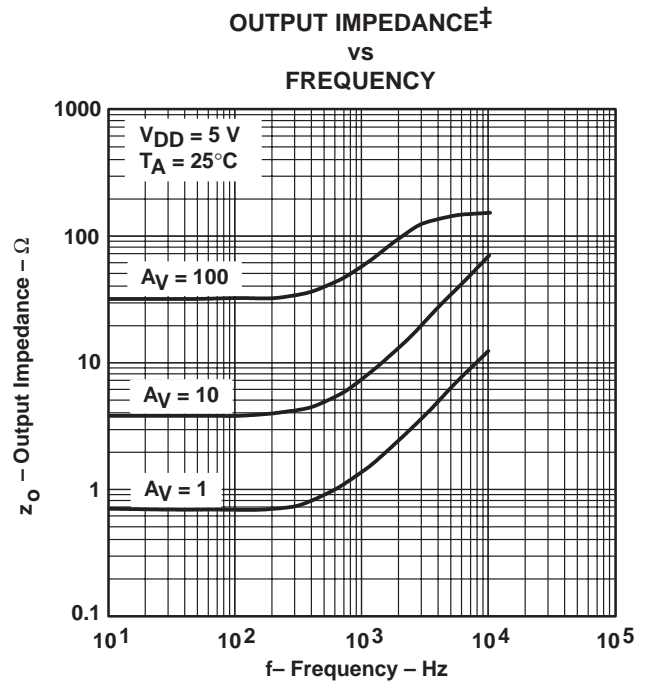
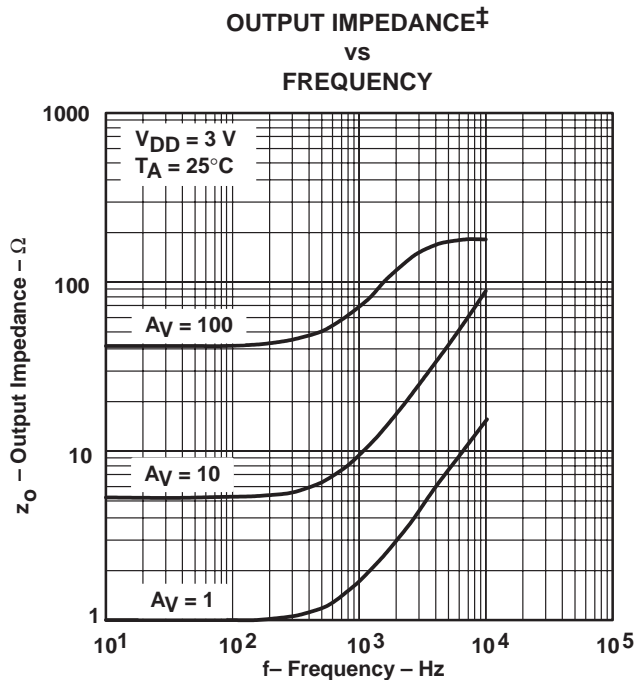
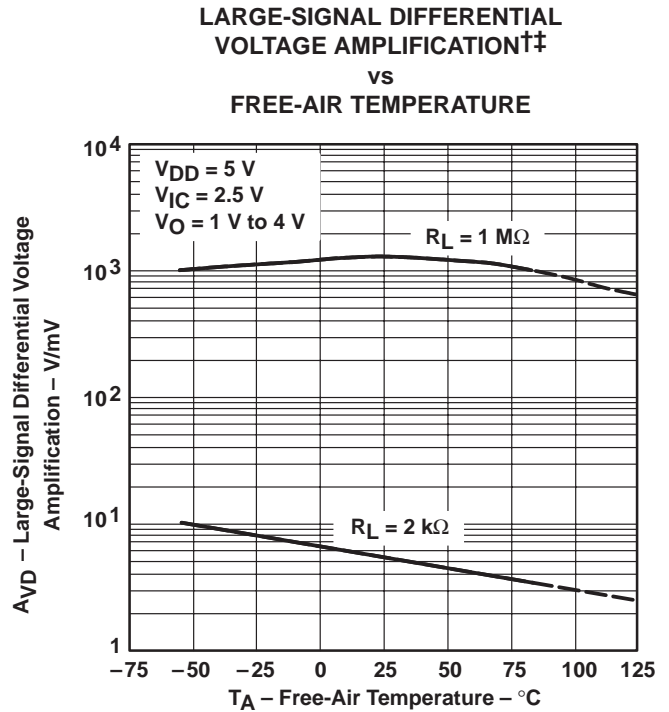
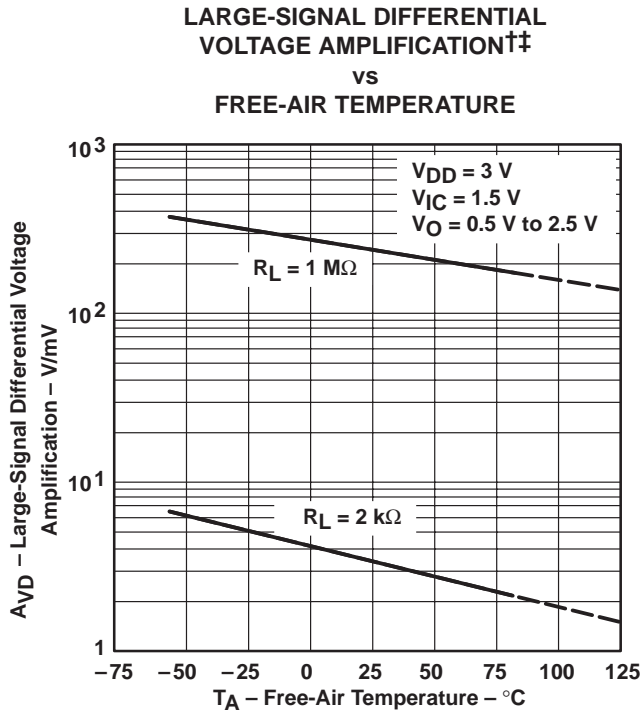


Figure 22

† For all curves where V<sub>DD</sub> = 5 V, all loads are referenced to 2.5 V. For all curves where V<sub>DD</sub> = 3 V, all loads are referenced to 1.5 V.



**TYPICAL CHARACTERISTICS**



† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.  
 ‡ For all curves where  $V_{DD} = 5\text{ V}$ , all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3\text{ V}$ , all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

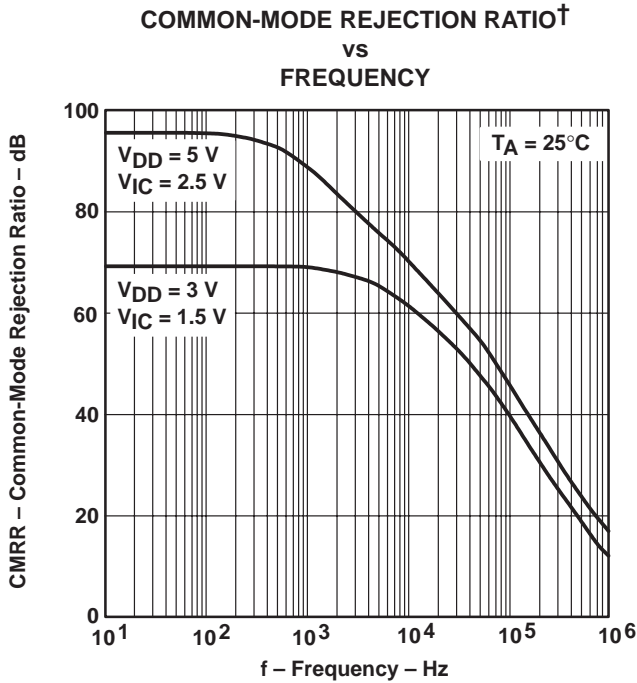


Figure 27

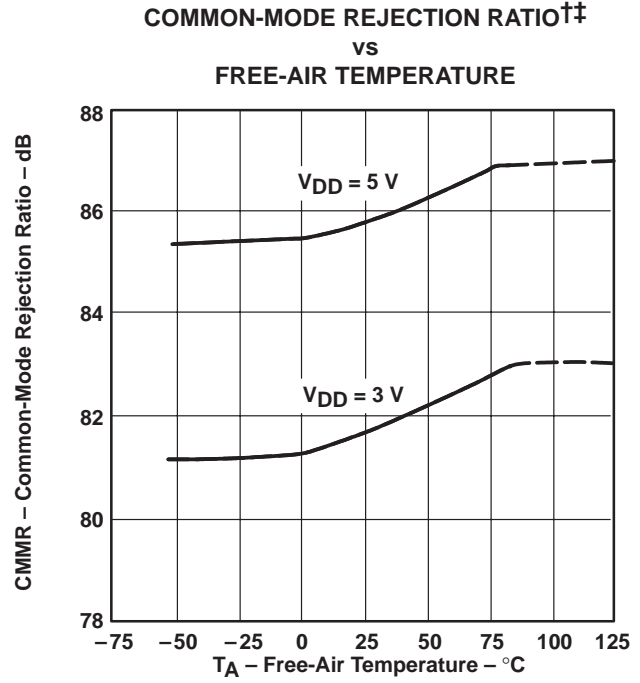


Figure 28

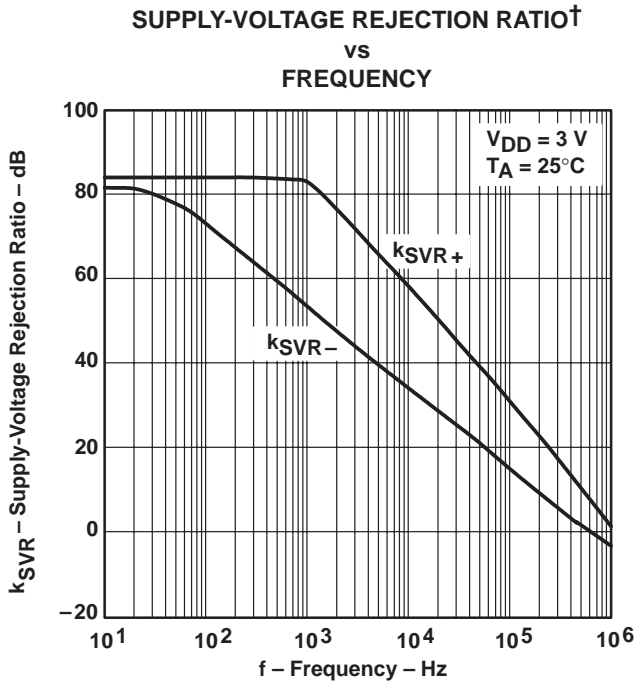


Figure 29

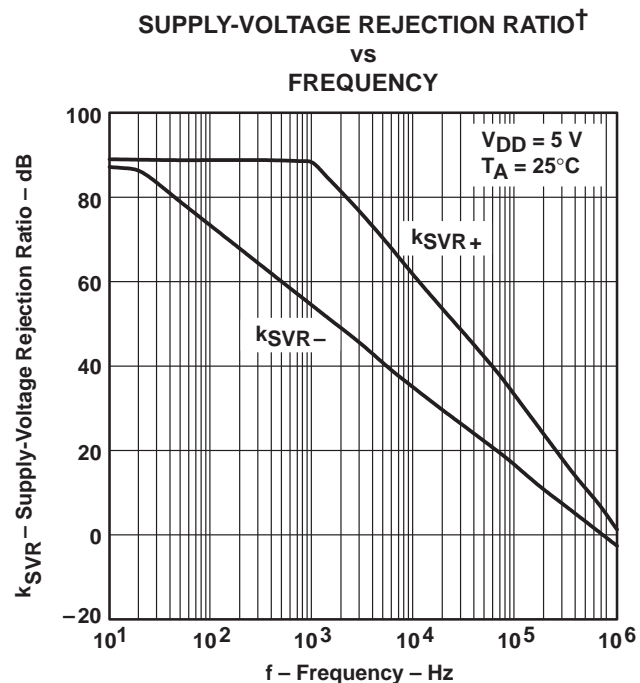
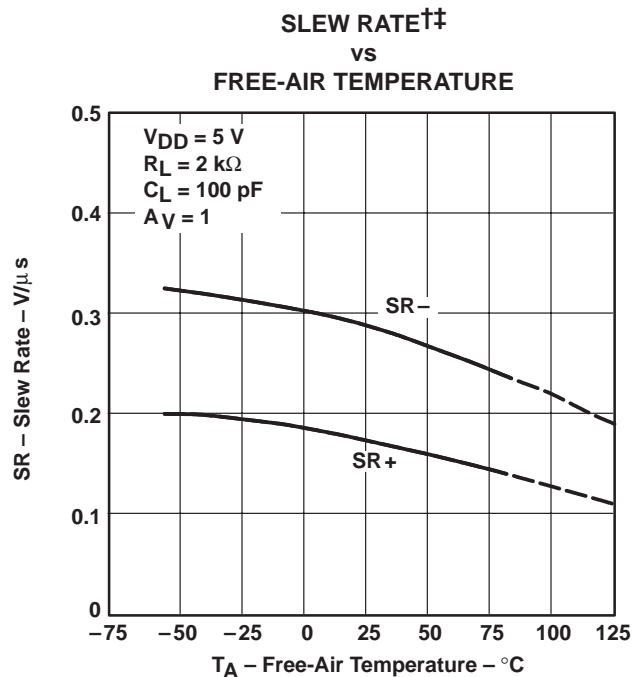
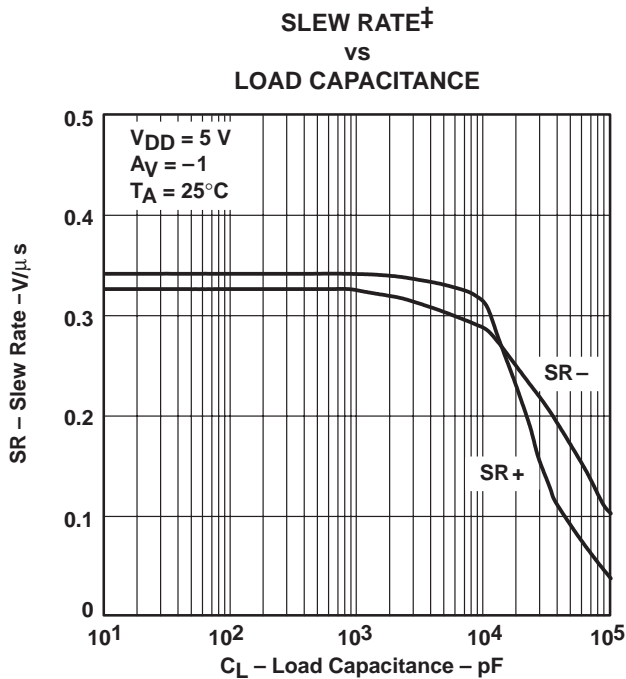
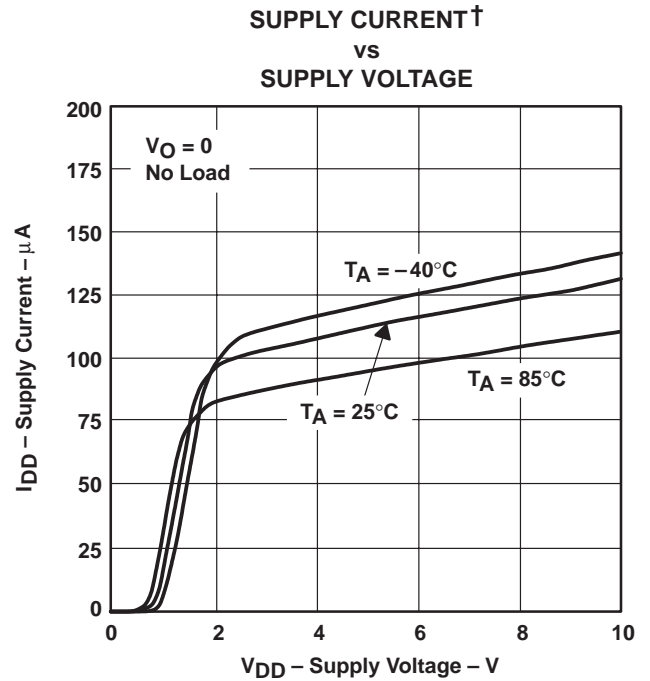
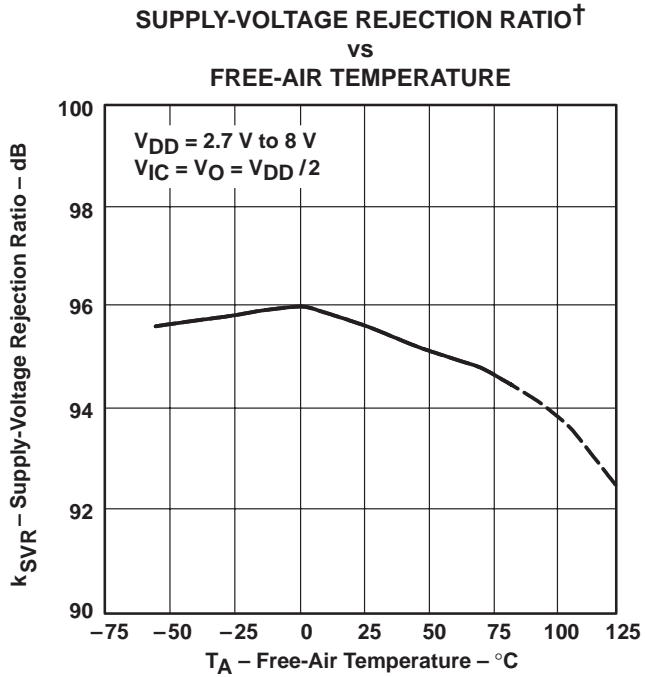


Figure 30

† For all curves where  $V_{DD} = 5\text{ V}$ , all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3\text{ V}$ , all loads are referenced to 1.5 V.  
 ‡ Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

**TYPICAL CHARACTERISTICS**



† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

‡ For all curves where  $V_{DD} = 5\text{ V}$ , all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3\text{ V}$ , all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

INVERTING LARGE-SIGNAL PULSE RESPONSE†

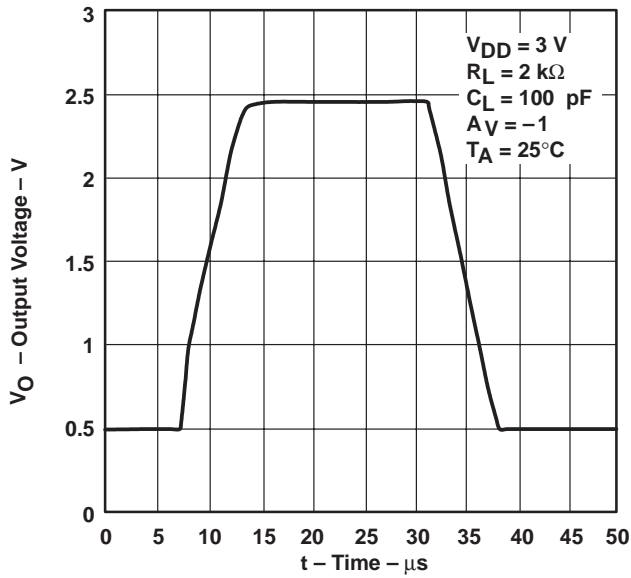


Figure 35

INVERTING LARGE-SIGNAL PULSE RESPONSE†

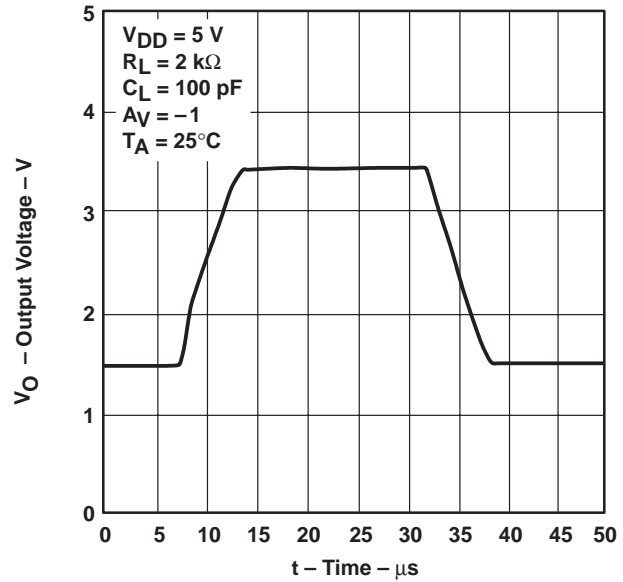


Figure 36

VOLTAGE-FOLLOWER LARGE-SIGNAL PULSE RESPONSE†

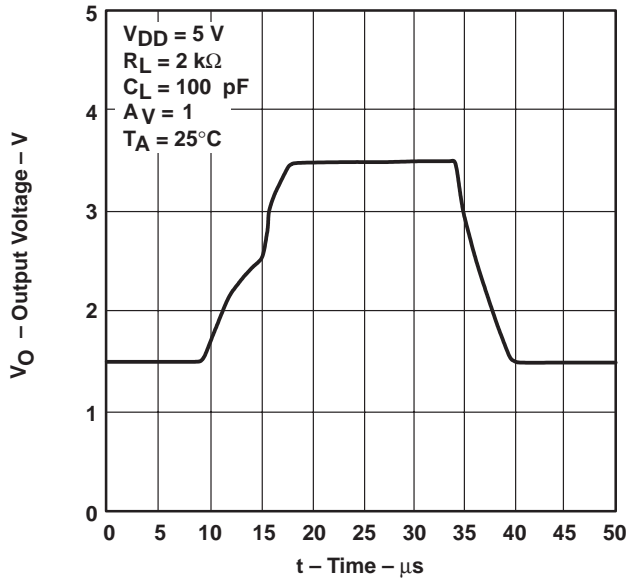


Figure 37

VOLTAGE-FOLLOWER LARGE-SIGNAL PULSE RESPONSE†

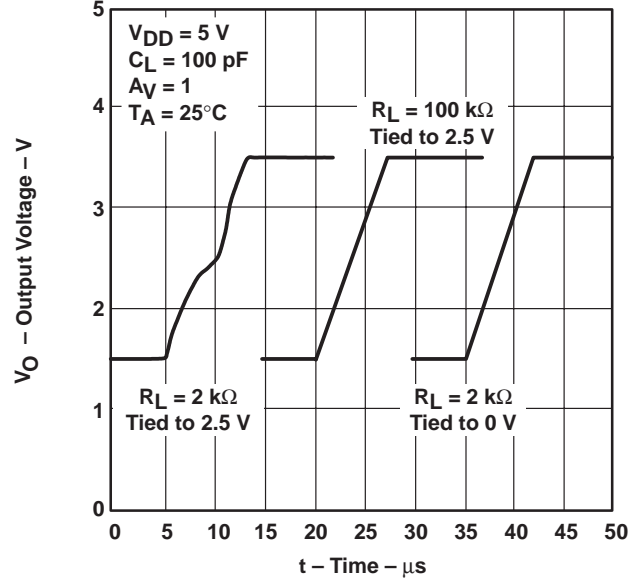
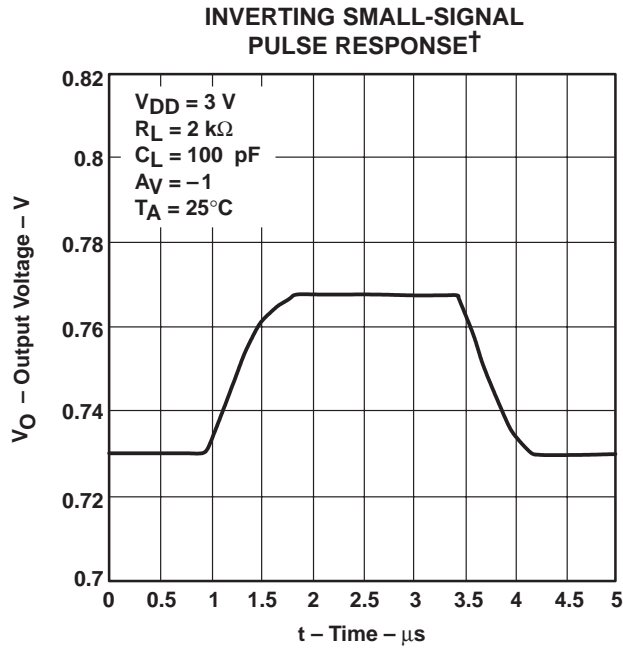


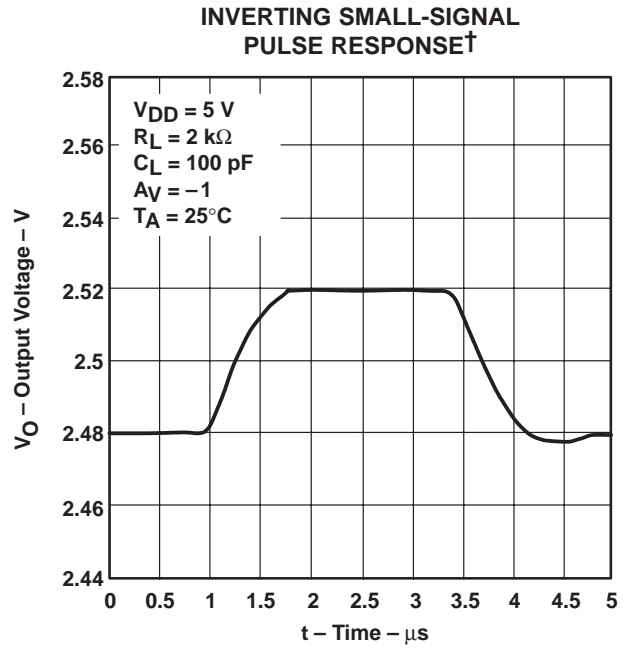
Figure 38

† For all curves where  $V_{DD} = 5\text{ V}$ , all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3\text{ V}$ , all loads are referenced to 1.5 V.

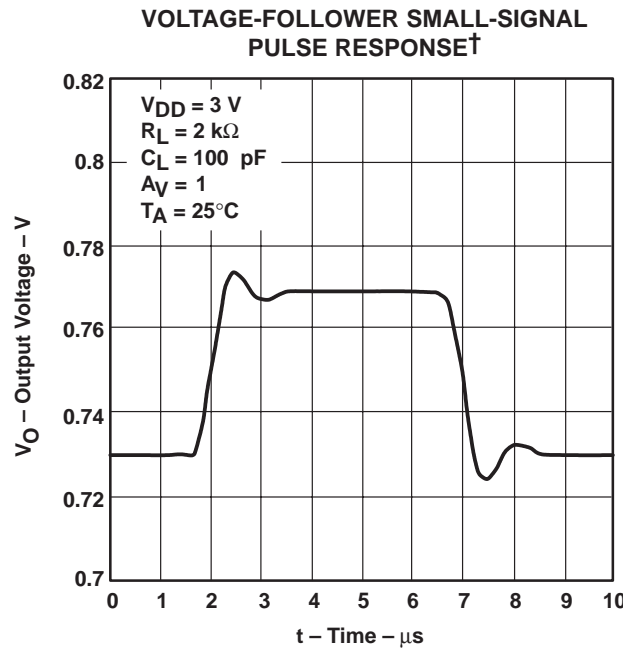
**TYPICAL CHARACTERISTICS**



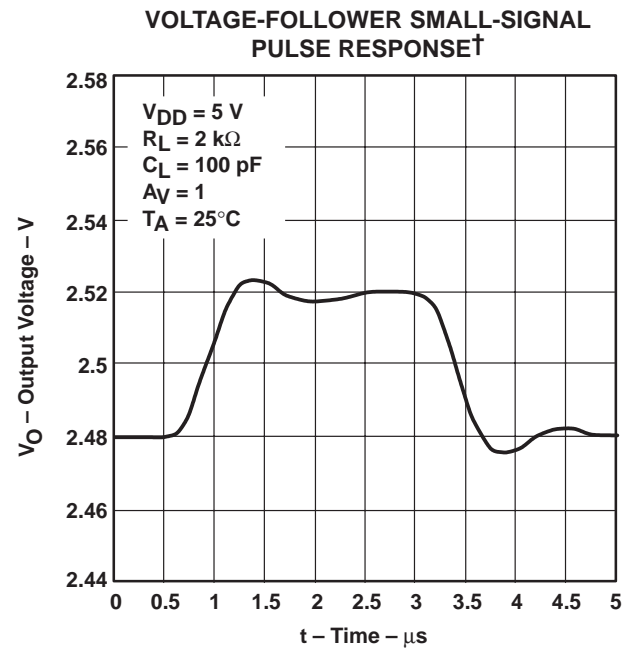
**Figure 39**



**Figure 40**



**Figure 41**



**Figure 42**

† For all curves where  $V_{DD} = 5\text{ V}$ , all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3\text{ V}$ , all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

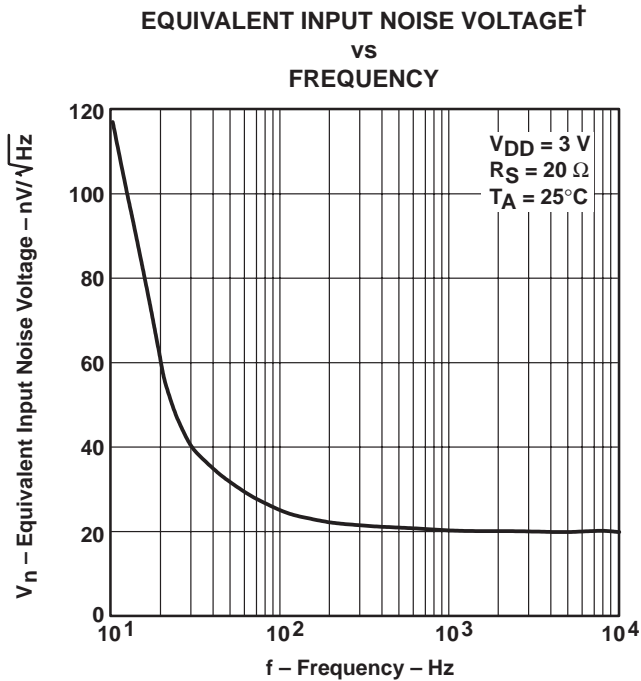


Figure 43

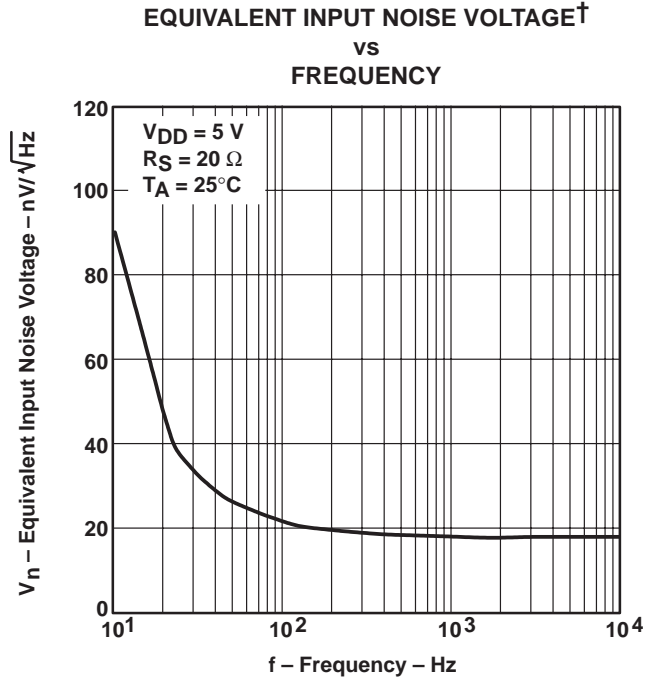


Figure 44

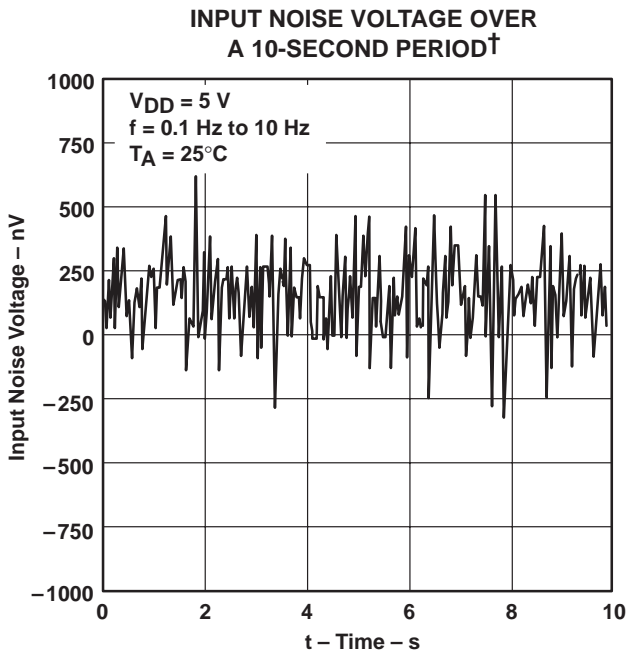


Figure 45

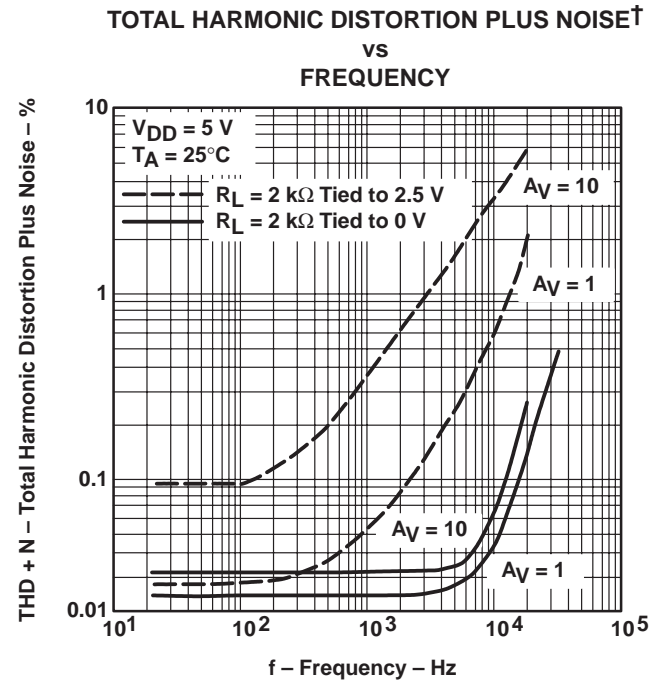


Figure 46

† For all curves where  $V_{DD} = 5\text{ V}$ , all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3\text{ V}$ , all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

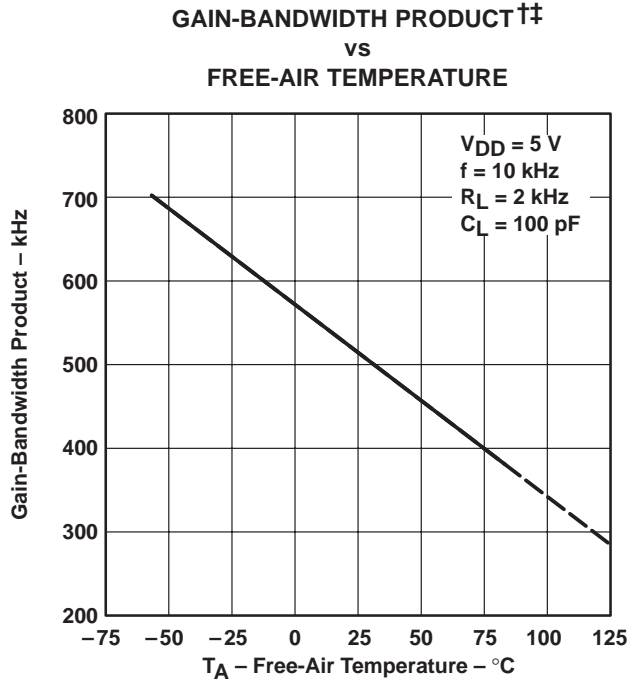


Figure 47

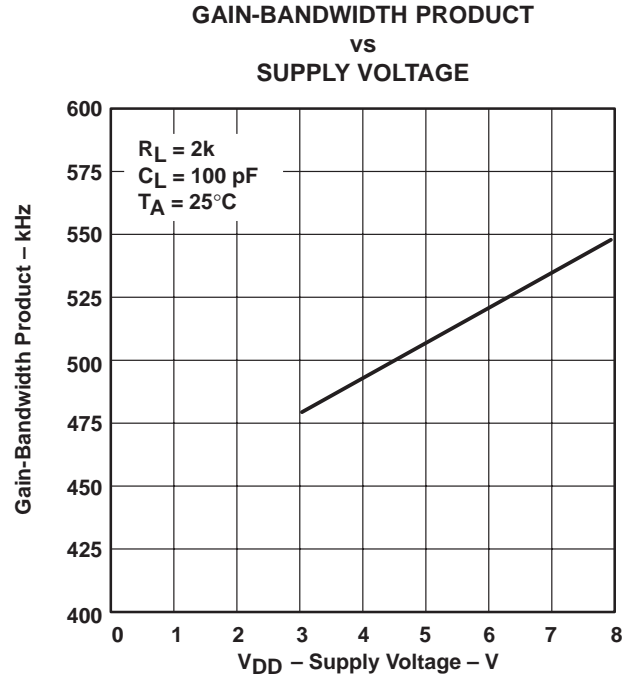


Figure 48

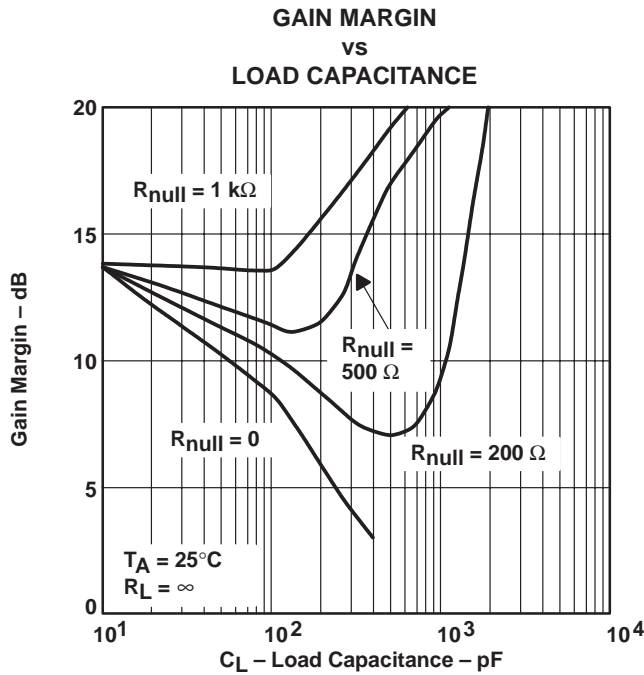


Figure 49

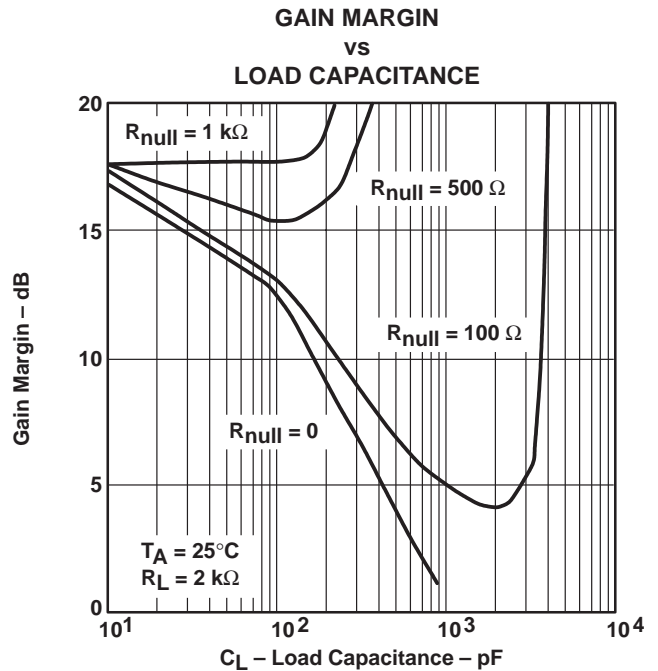


Figure 50

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.  
 †† For all curves where  $V_{DD} = 5\text{ V}$ , all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3\text{ V}$ , all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

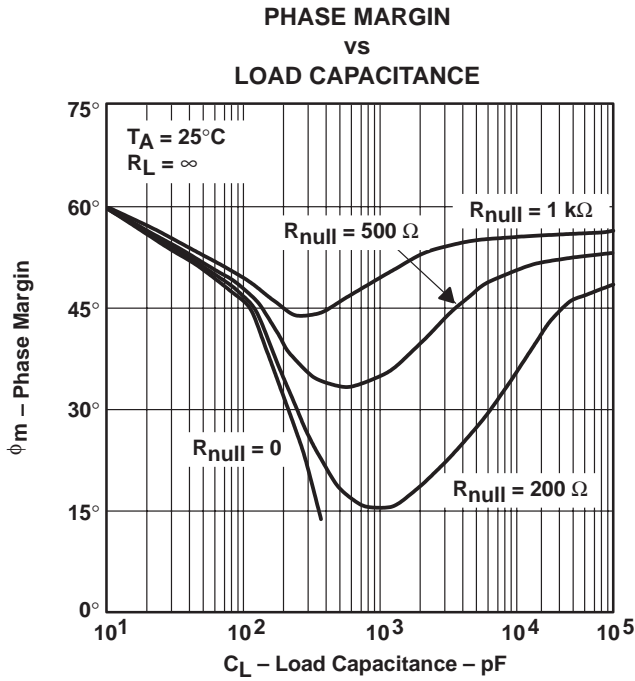


Figure 51

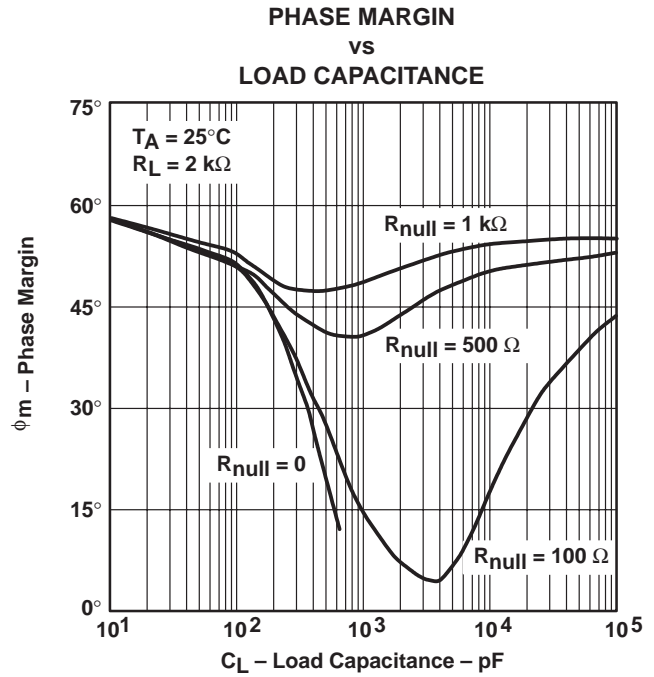


Figure 52

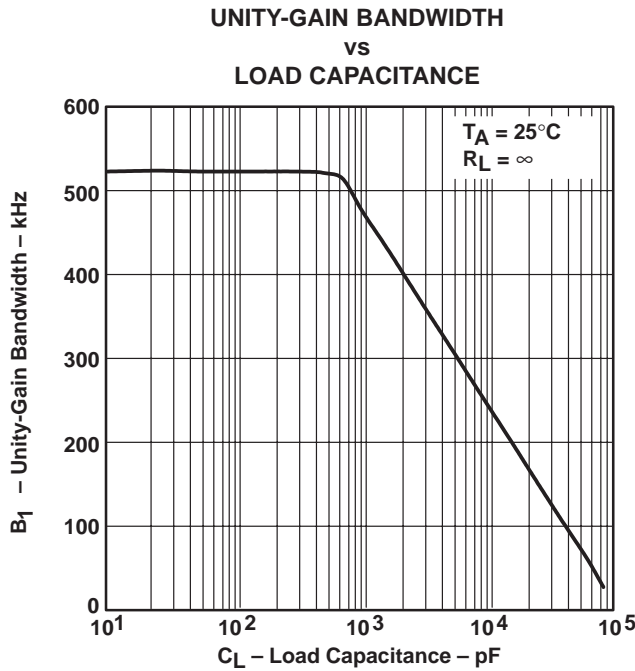


Figure 53

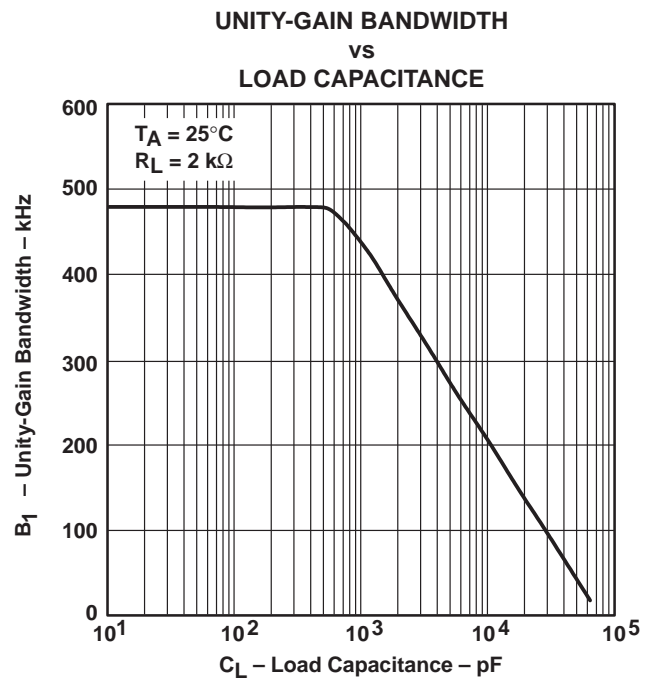


Figure 54



## APPLICATION INFORMATION

### driving large capacitive loads

The TLV2721 is designed to drive larger capacitive loads than most CMOS operational amplifiers. Figure 50 through Figure 55 illustrate its ability to drive loads greater than 100 pF while maintaining good gain and phase margins ( $R_{null} = 0$ ).

A small series resistor ( $R_{null}$ ) at the output of the device (Figure 55) improves the gain and phase margins when driving large capacitive loads. Figure 50 through Figure 53 show the effects of adding series resistances of 100  $\Omega$ , 200  $\Omega$ , 500  $\Omega$ , and 1 k $\Omega$ . The addition of this series resistor has two effects: the first effect is that it adds a zero to the transfer function and the second effect is that it reduces the frequency of the pole associated with the output load in the transfer function.

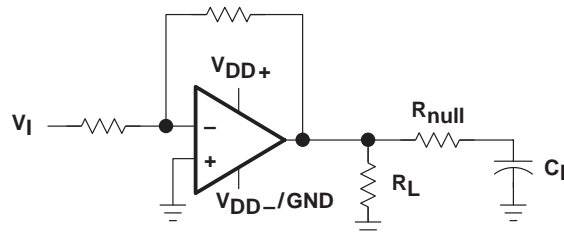
The zero introduced to the transfer function is equal to the series resistance times the load capacitance. To calculate the approximate improvement in phase margin, equation 1 can be used.

$$\Delta\phi_{m1} = \tan^{-1} \left( 2 \times \pi \times \text{UGBW} \times R_{null} \times C_L \right) \quad (1)$$

where :

- $\Delta\phi_{m1}$  = improvement in phase margin
- UGBW = unity-gain bandwidth frequency
- $R_{null}$  = output series resistance
- $C_L$  = load capacitance

The unity-gain bandwidth (UGBW) frequency decreases as the capacitive load increases (Figure 54 and Figure 55). To use equation 1, UGBW must be approximated from Figure 54 and Figure 55.



**Figure 55. Series-Resistance Circuit**

The TLV2721 is designed to provide better sinking and sourcing output currents than earlier CMOS rail-to-rail output devices. This device is specified to sink 500  $\mu\text{A}$  and source 1 mA at  $V_{DD} = 5\text{ V}$  at a maximum quiescent  $I_{DD}$  of 200  $\mu\text{A}$ . This provides a greater than 80% power efficiency.

When driving heavy dc loads, such as 2 k $\Omega$ , the positive edge under slewing conditions can experience some distortion. This condition can be seen in Figure 38. This condition is affected by three factors:

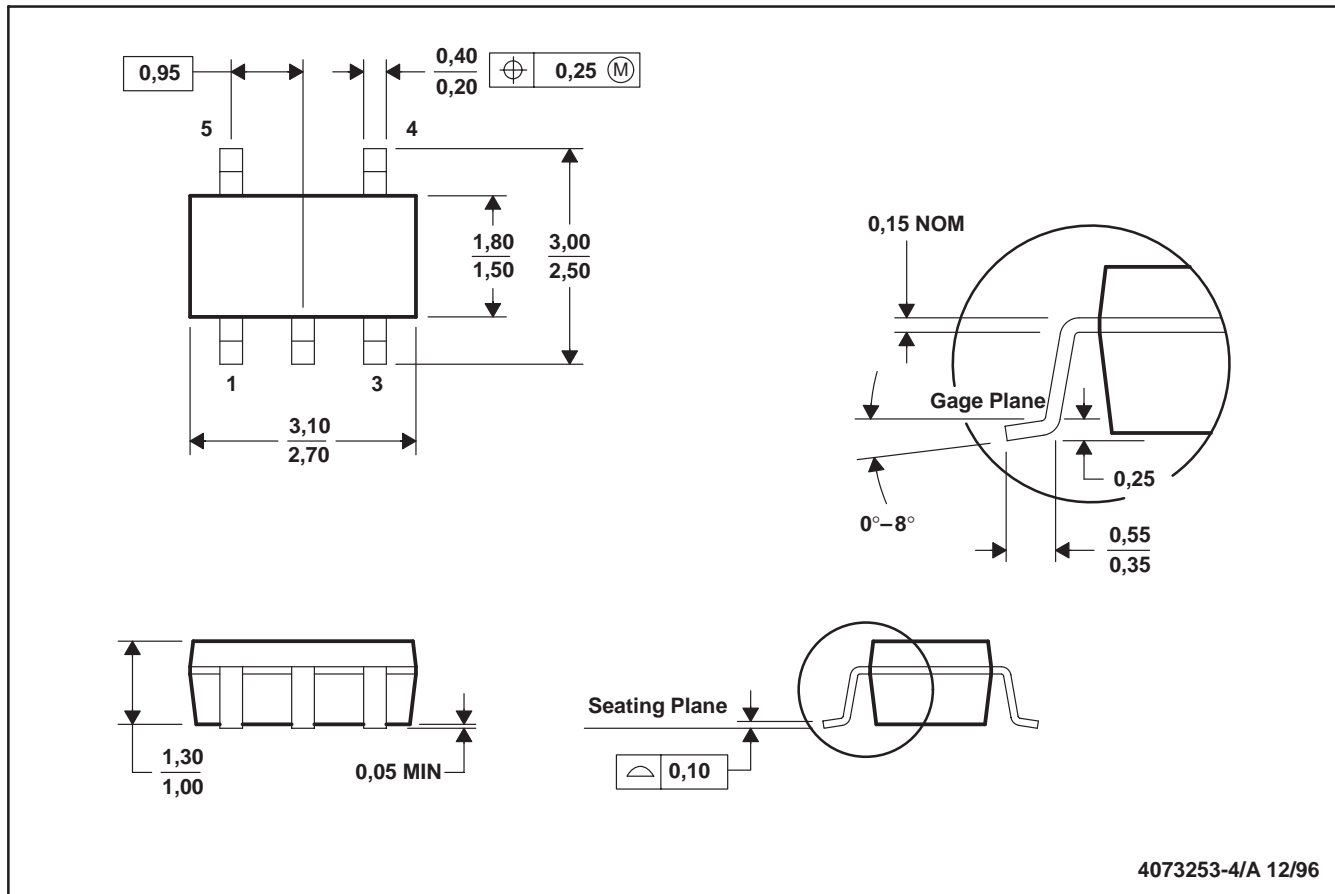
- Where the load is referenced. When the load is referenced to either rail, this condition does not occur. The distortion occurs only when the output signal swings through the point where the load is referenced. Figure 39 illustrates two 2-k $\Omega$  load conditions. The first load condition shows the distortion seen for a 2-k $\Omega$  load tied to 2.5 V. The third load condition in Figure 39 shows no distortion for a 2-k $\Omega$  load tied to 0 V.
- Load resistance. As the load resistance increases, the distortion seen on the output decreases. Figure 39 illustrates the difference seen on the output for a 2-k $\Omega$  load and a 100-k $\Omega$  load with both tied to 2.5 V.
- Input signal edge rate. Faster input edge rates for a step input result in more distortion than with slower input edge rates.



**MECHANICAL INFORMATION**

**DBV (R-PDSO-G5)**

**PLASTIC SMALL-OUTLINE PACKAGE**



4073253-4/A 12/96

- NOTES: A. All linear dimensions are in millimeters.  
 B. This drawing is subject to change without notice.  
 C. Body dimensions include mold flash or protrusion.

## **IMPORTANT NOTICE**

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

**CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.**

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.